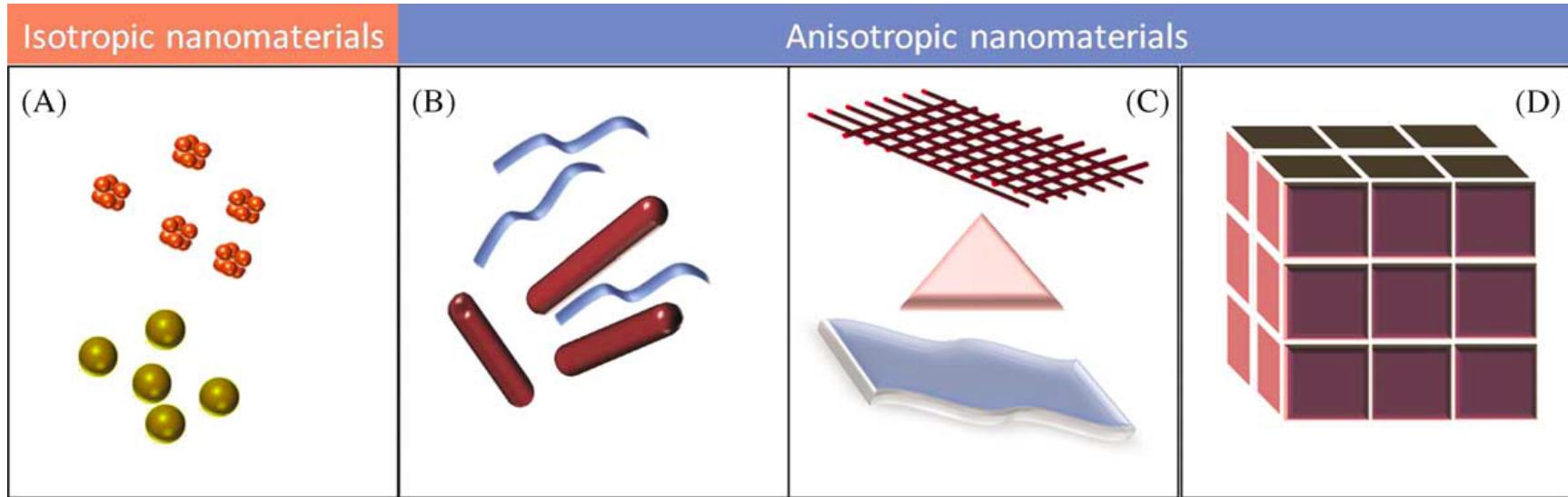
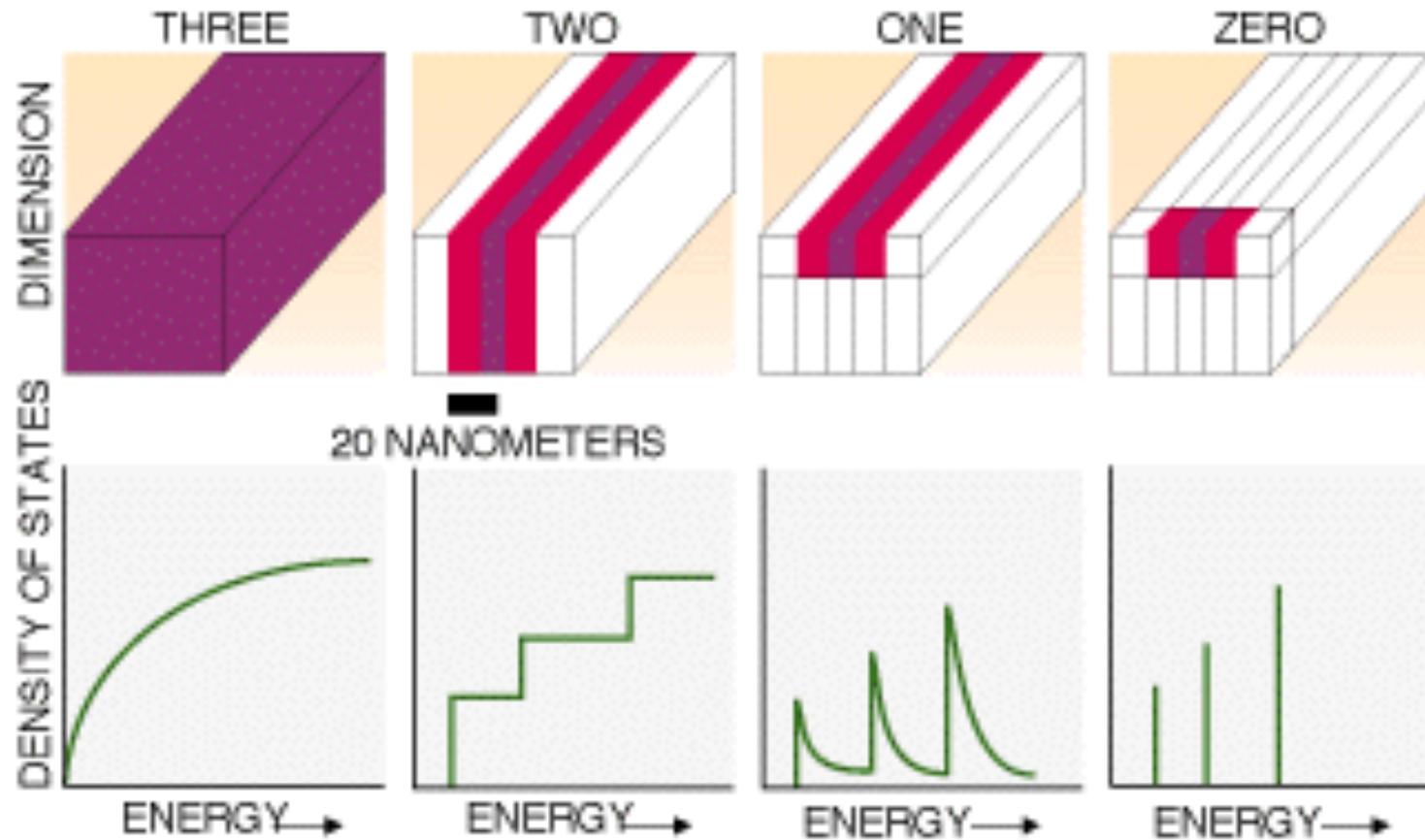


# Growth of Nanostructures



Various kinds of nanomaterials

# Quantum confinement



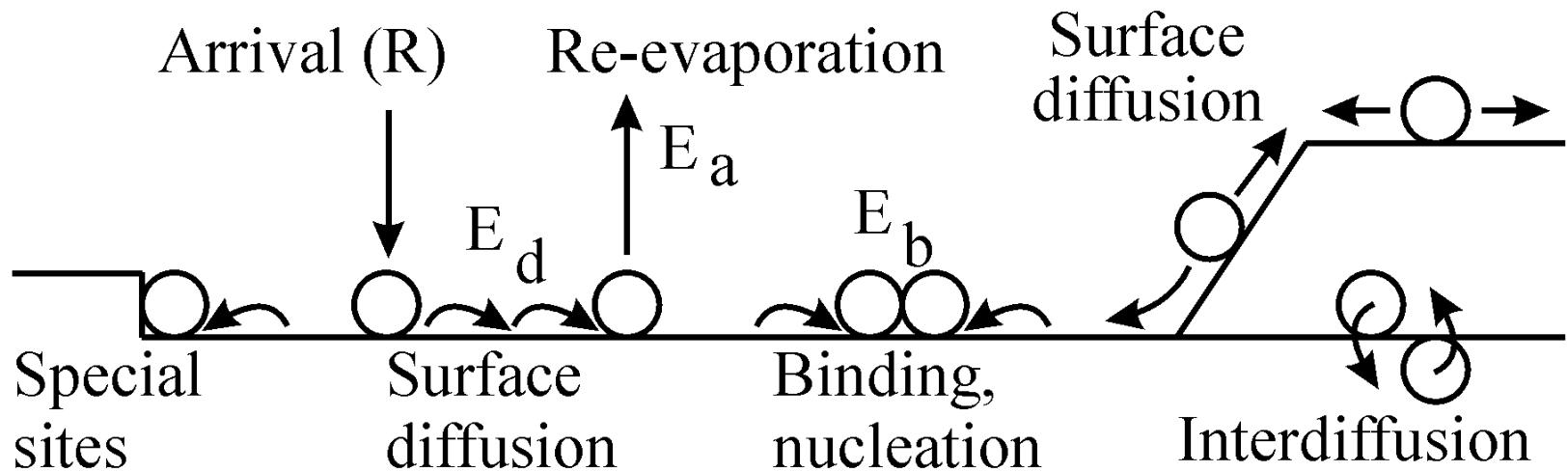
(Scientific American)

# Growth kinetics

- Schematic description: particles are deposited on a surface and become adsorbed (adatoms). They diffuse around the surface and can be bound to the surface. Vice versa, unbinding and desorption happens.
- The kinetics of epitaxial growth is determined by the surface diffusion and nucleation.

Diffusion → Nucleation → Growth

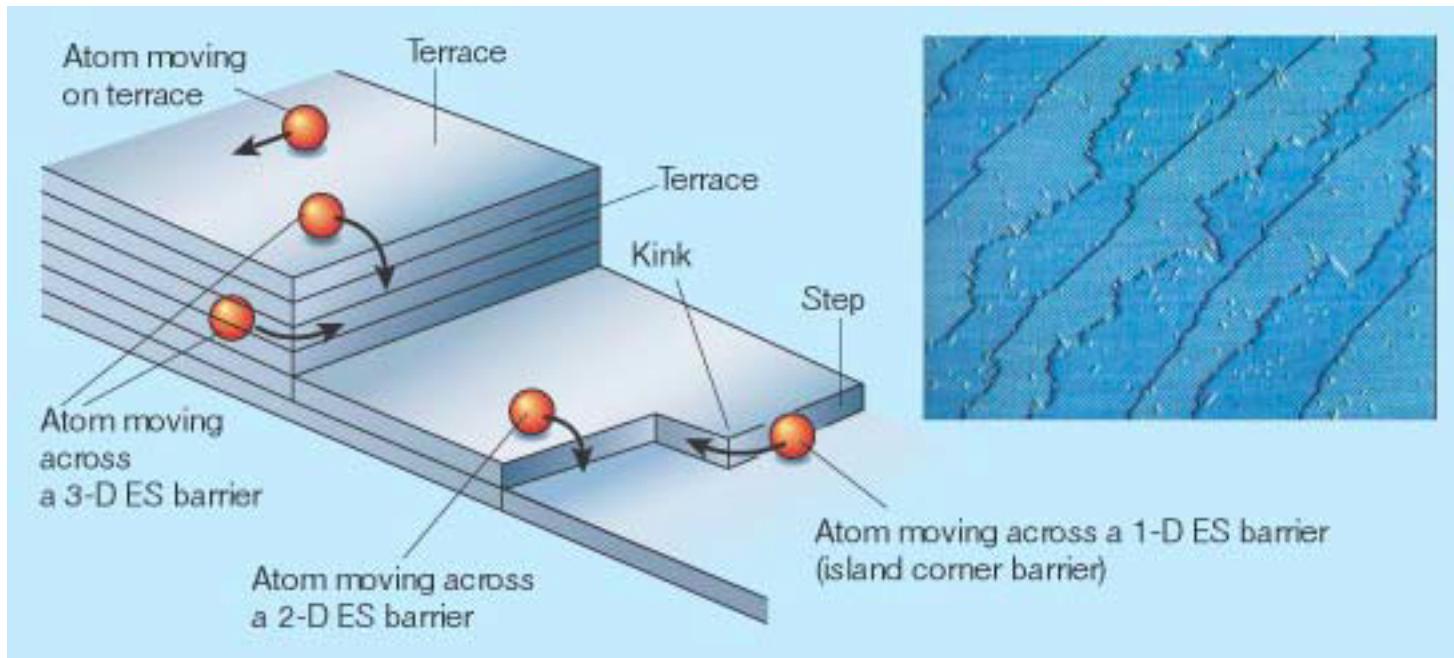
# Atomic-level processes



**Variables:**  $R$  (or  $F$ ),  $T$ , time sequences ( $t$ )

**Parameters:**  $E_a$ ,  $E_d$ ,  $E_b$ , mobility, defects...

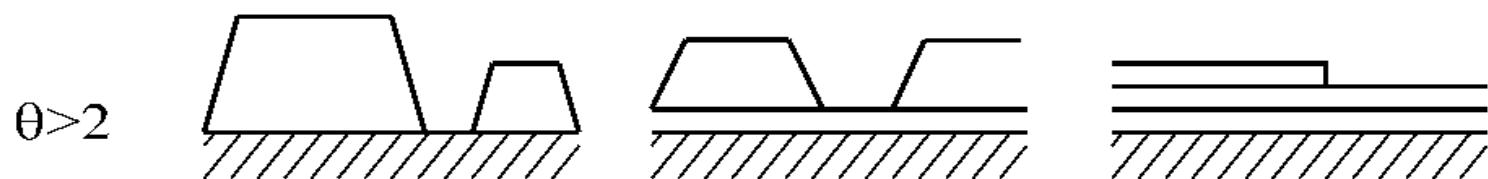
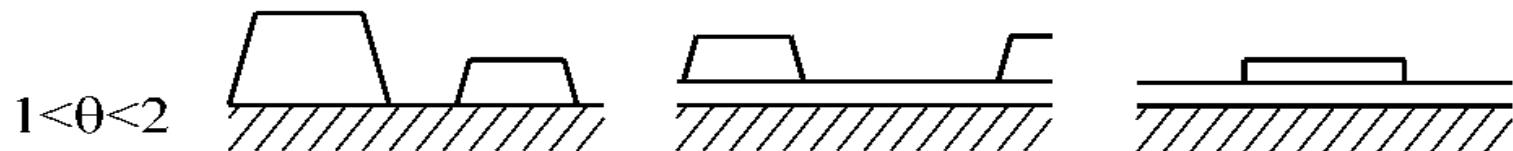
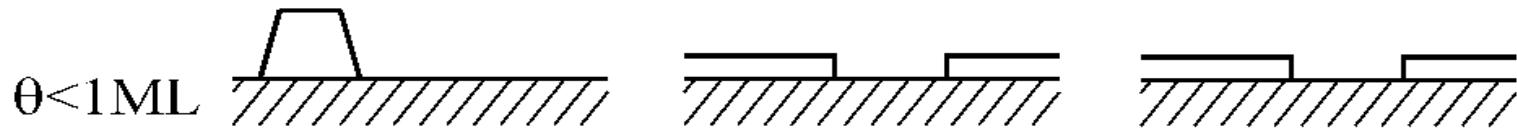
# Atomistic Models for Crystalline Surfaces



## Terrace Step Kink (TSK) model

Phase growth or transition simply involves the ***bond forming*** and ***bond breaking***

# Growth modes



(a)

(b)

(c)

Island

*Volmer-Weber*

Layer + Island

*Stranski-Krastanov*

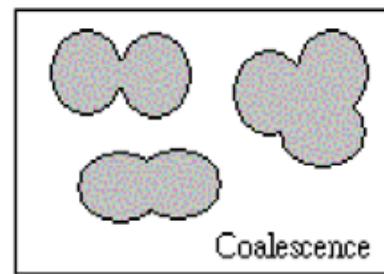
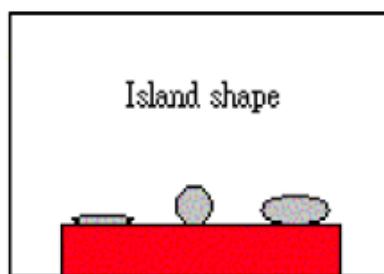
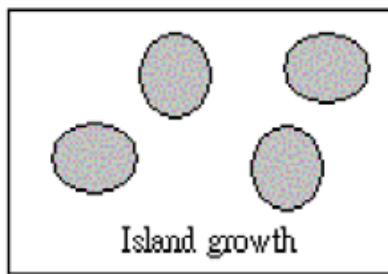
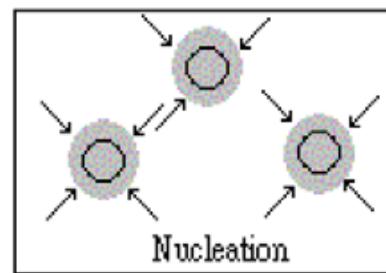
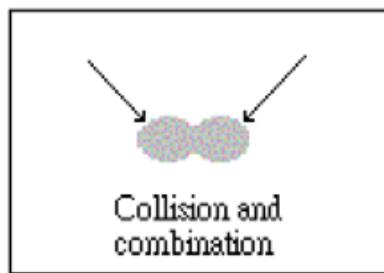
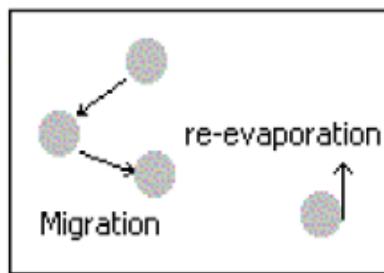
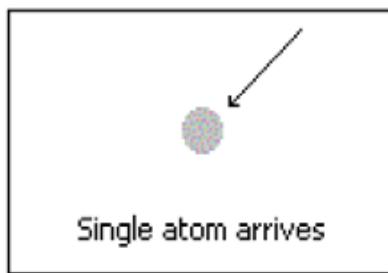
Layer

*Frank-VdM*

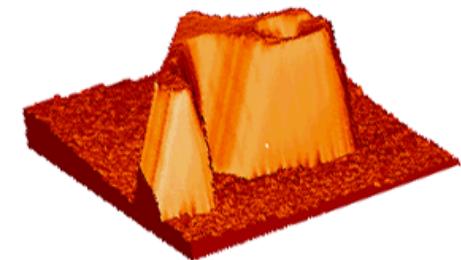
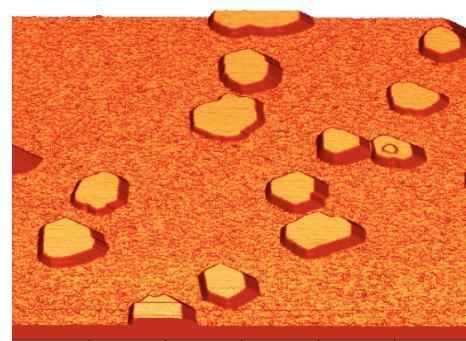
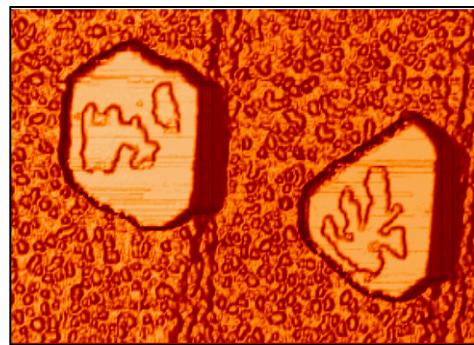
$$\gamma_s < \gamma_f + \gamma_i$$

$$\gamma_s \geq \gamma_f + \gamma_i$$

# Thin Film Growth Process



# Growth modes at diff. $T$



Non-crystalline

2D islands

3D islands

150 K

300 K

# Epitaxial Growth

Epitaxial films take on a lattice structure and orientation identical to those of the substrate.

- **Homoepitaxy:** a crystalline film is grown on a substrate or film of the same material.
- **Heteroepitaxy:** a crystalline film grows on a crystalline substrate or film of a different material.

# Techniques for making nanowires

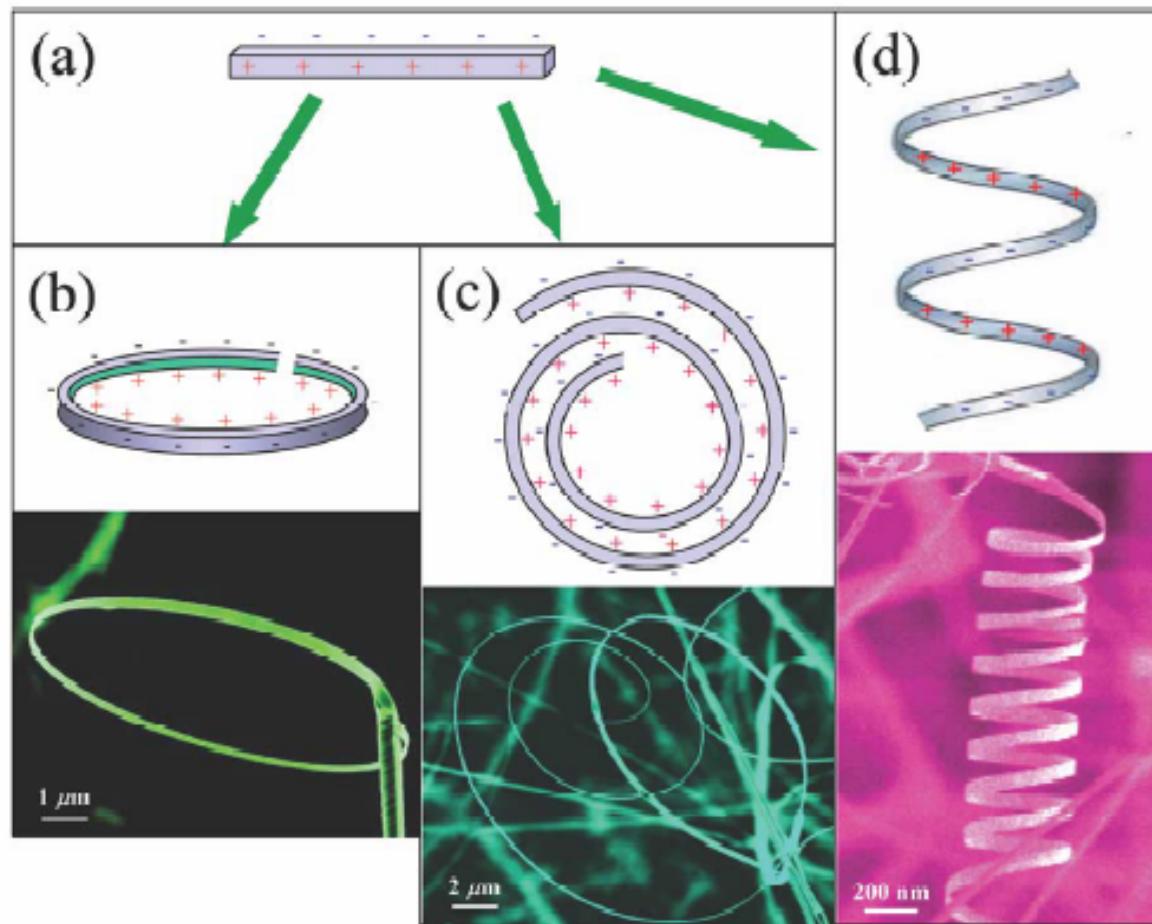
- **Spontaneous growth:**
  - Evaporation condensation
  - Dissolution condensation
  - Vapor-Liquid-Solid growth (VLS)
  - Stress induced re-crystallization
- **Template-based synthesis:**
  - Electrochemical deposition
  - Electrophoretic deposition
  - Colloid dispersion, melt, or solution filling
  - Conversion with chemical reaction
- **Electro-spinning**
- **Lithography** (*top-down*)

# General characters for spontaneous growth

- Anisotropic growth is required
- Crystal growth proceeds along one direction, whereas there is no growth along other direction.
- Uniformly sized nanowires (i.e. the same diameter along the longitudinal direction of a given nanowire)

# Vapor-Solid (VS) technique

- Nanowires and nanorods grown by this method are commonly single crystals with fewer imperfections
- The formation of nanowires or nanorods is due to the anisotropic growth.
- The general idea is that the different facets in a crystal have different growth rates
- There is no control on the direction of growth of nanowire in this method



***“Nanostructures of zinc oxide,” by Zhon Lin Wang***

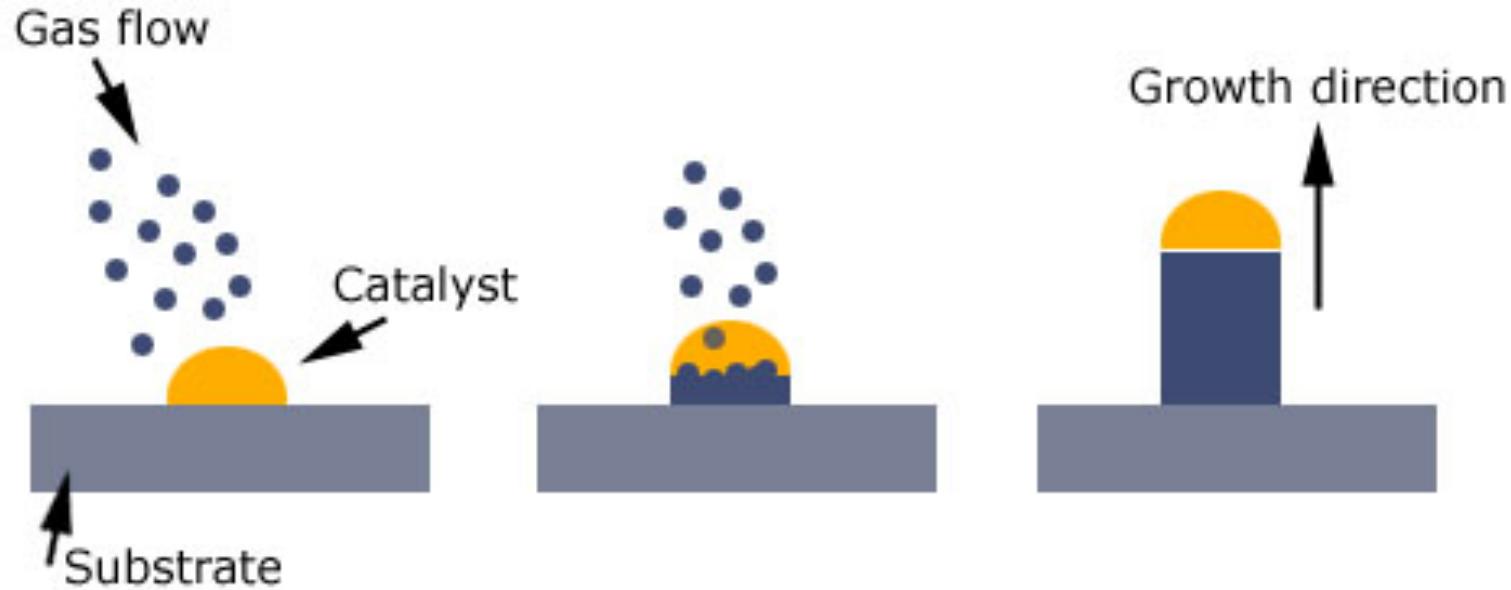
# Vapor Liquid Solid Growth (VLS)

## General Idea:

A second phase material, commonly referred to as **catalyst**, is introduced to direct and confine the crystal growth on a specific orientation and within a confined area.

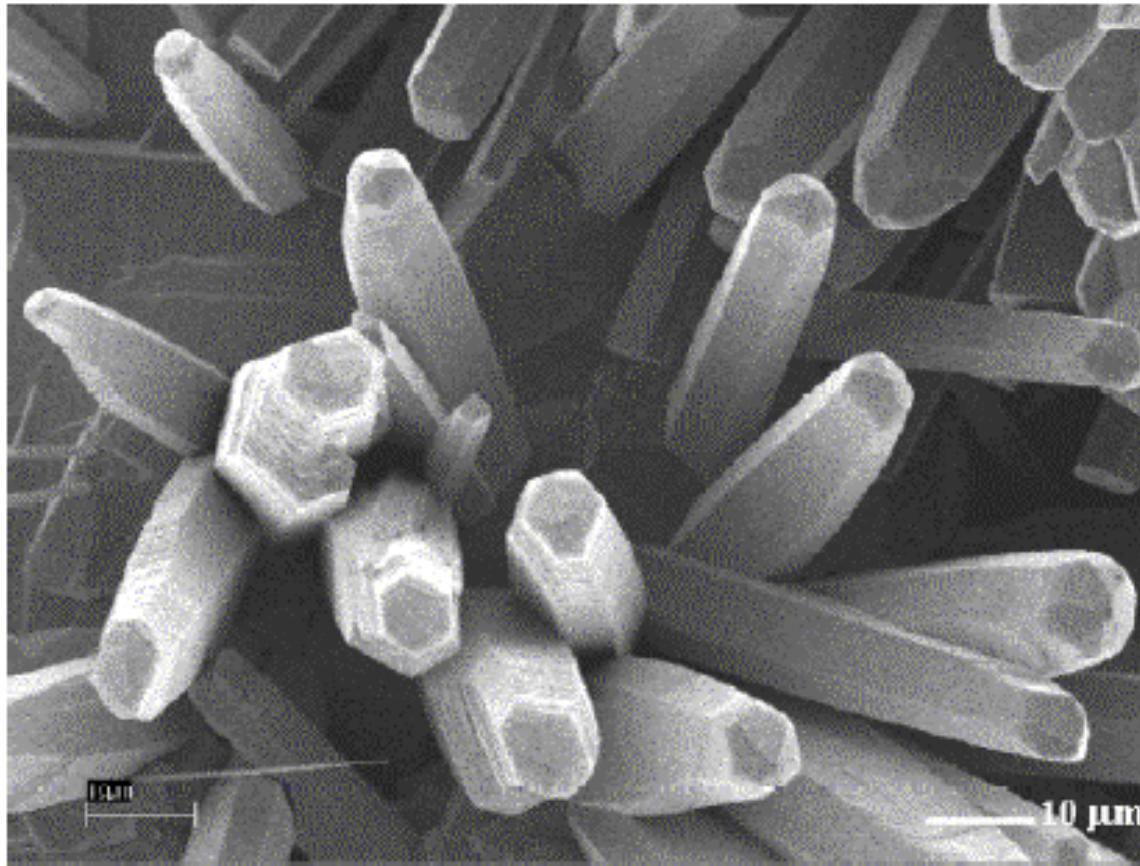
- Catalyst forms a **liquid droplet** by itself
- Acts as a trap for growth species
- The growth species is evaporated first and then diffuses and dissolves into a liquid droplet
- It precipitates at the interface between the substrate and the liquid

# VLS Growth



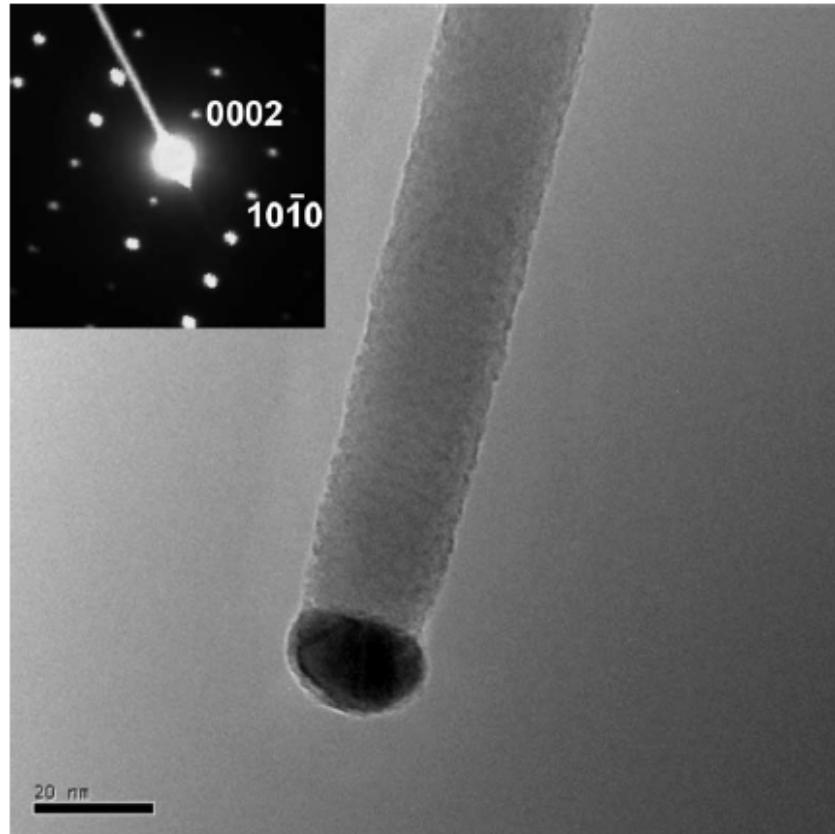
Growth species in the catalyst droplets subsequently precipitates at the growth surface resulting in the ***one-directional growth***

# VLS Growth



*“A Non-Traditional Vapor-Liquid-Solid Method for Bulk Synthesis of Semiconductor Nanowires,”* Shashank Sharma, and Mahendra K. Sunkara

# VLS Growth



TEM and selected area diffraction image of a single crystal ZnO nanorod. ( $\sim 20$  nm width).

***“ZnO nanowire growth and devices,” Y.W. Heo, D.P. Norton, et al.***

# Surface Energy

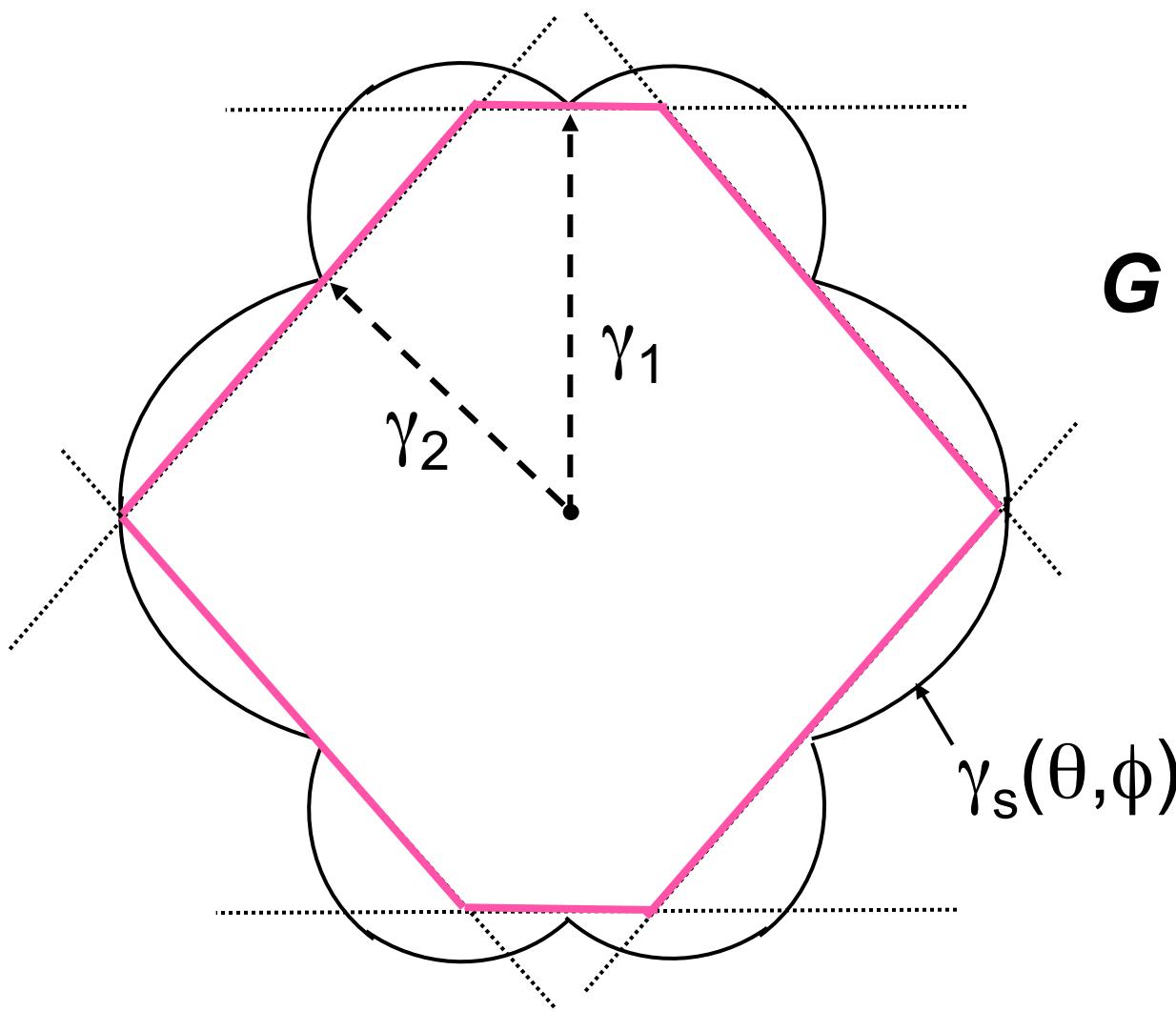
- Surface energy is given by

$$E(\Gamma) = \int_{\Gamma} \gamma \, dS$$

- Standard model for anisotropic surface free energy

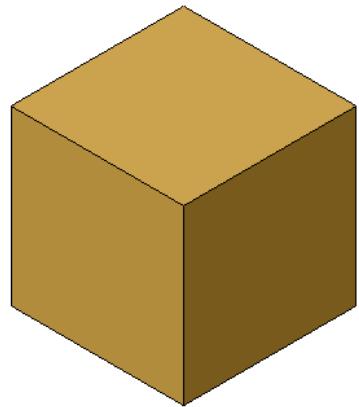
$$\gamma = \gamma_0(n)$$

## Wulff construction

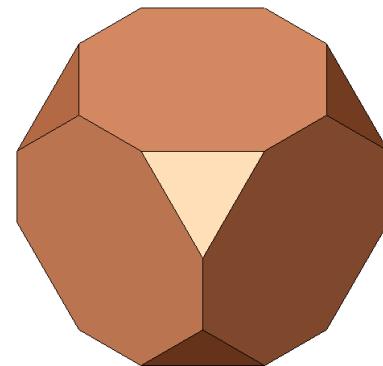


$$G = \int \gamma_s(\theta, \phi) dA$$

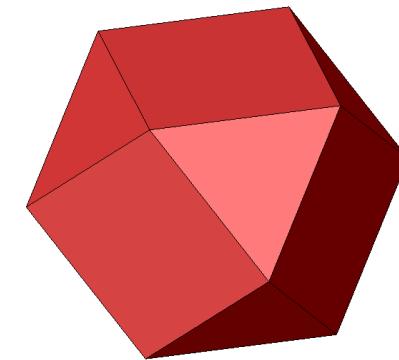
## Single crystalline structures



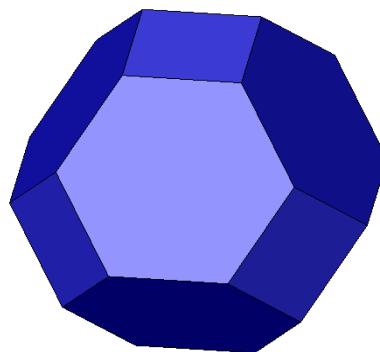
(a) cube



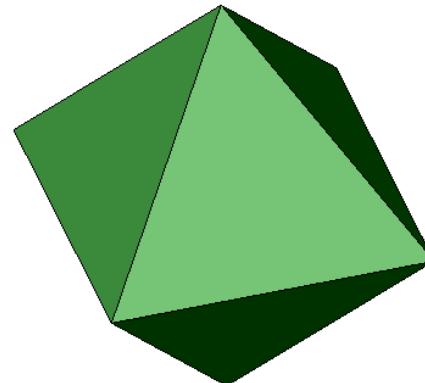
(b) truncated cube



(c) cuboctahedron

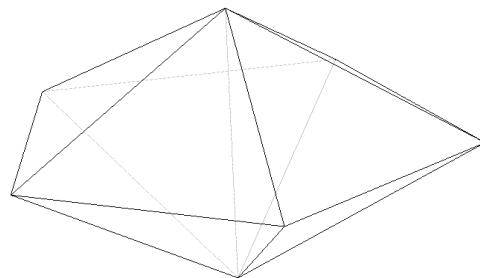
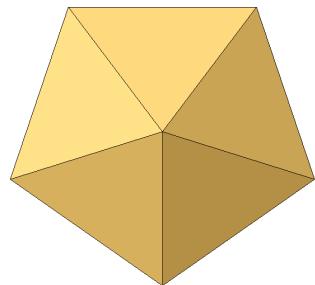


(d) truncated octahedron

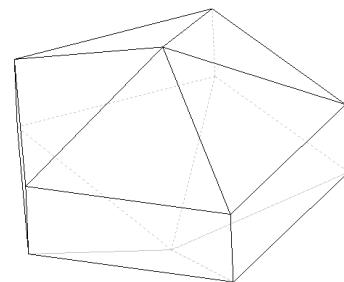
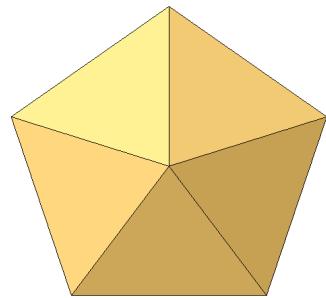


(e) octahedron

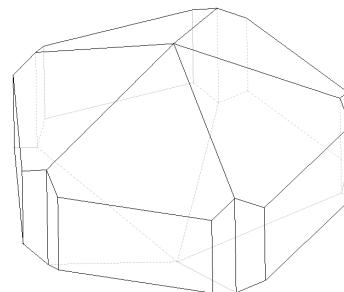
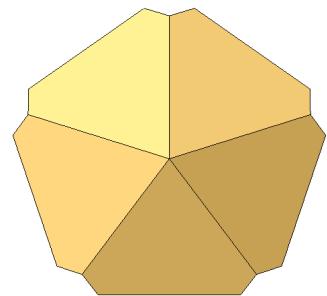
# Decahedra



**Classic**

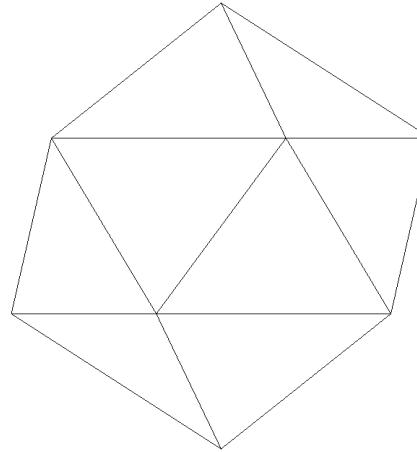
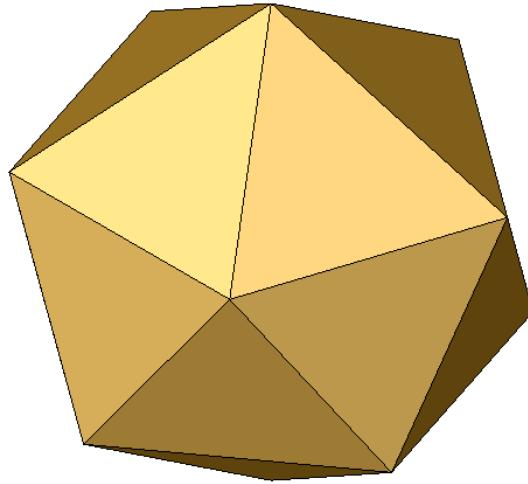


**Ino's**



**Marks'**

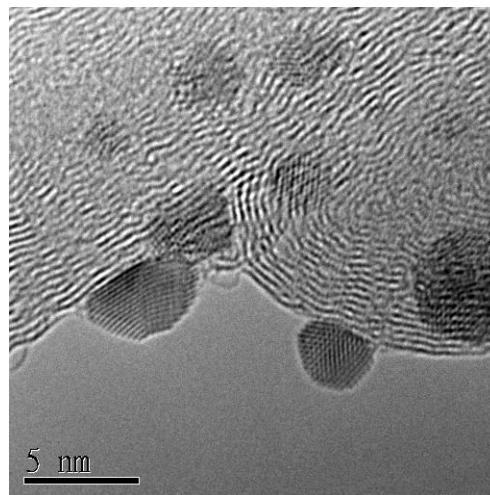
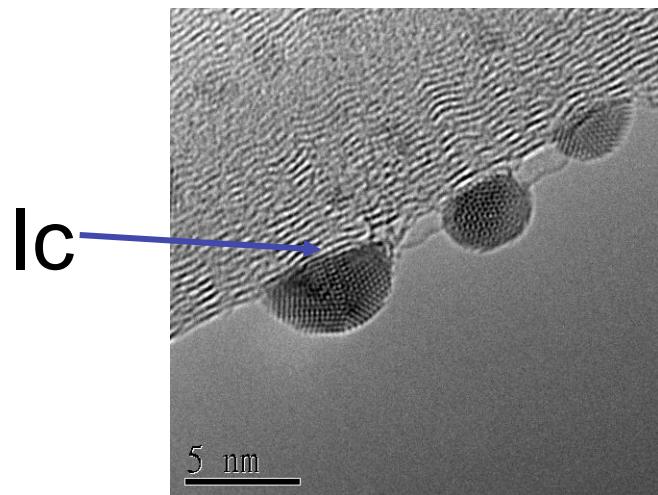
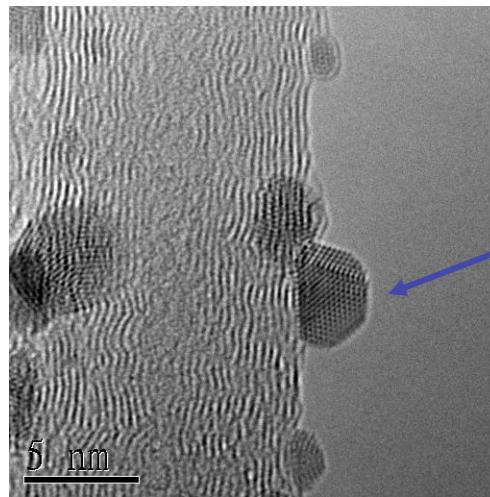
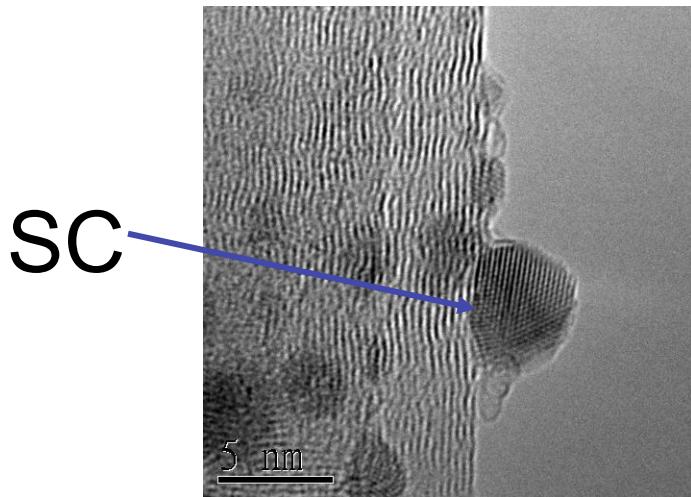
## Icosahedra



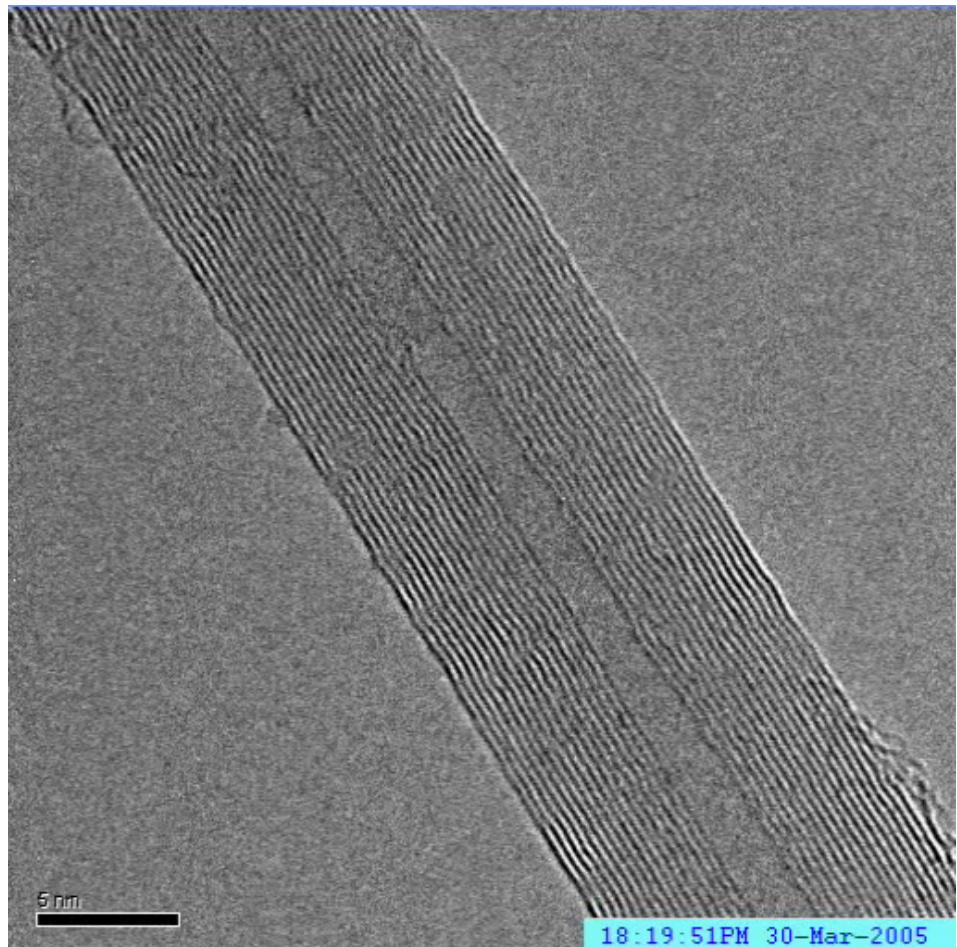
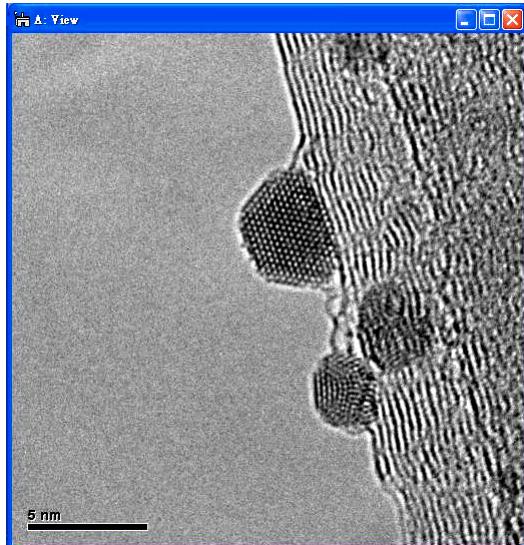
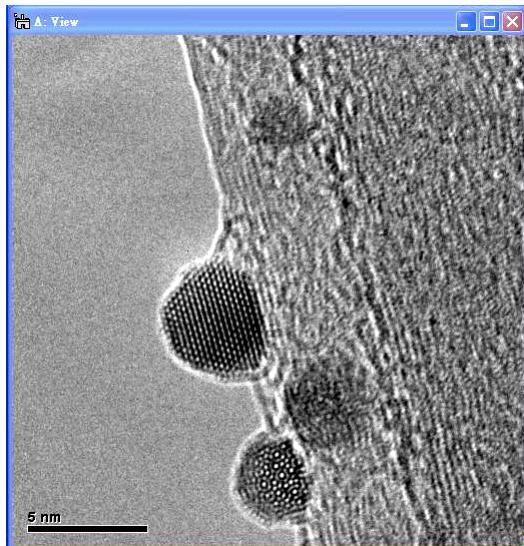
Size-dependent structures calculated for Ni clusters:  
Icosahedra for 142 – 2300 atoms;  
Marks' decahedra for 2300 – 17000 atoms;  
Single crystal for > 17000 atoms.

C.L. Cleveland and Uzi Landman, J. Chem. Phys. 94, 7376 (1991)

# Varying structures of Ag clusters

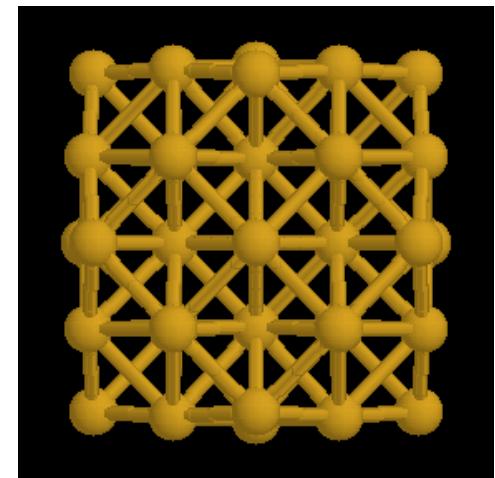
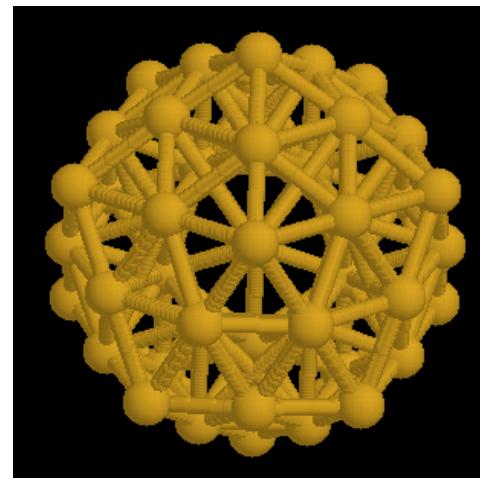
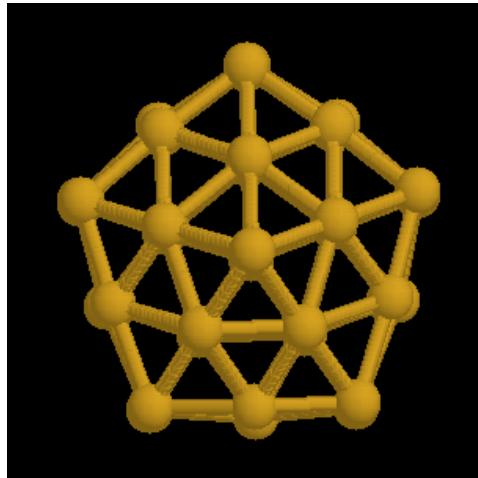


# Atomic motion and recrystallization



Room temperature

## Possible shell structures of nano particles



Decahedr  
al:

10 (111)

faces +

(Courtesy of C.M. Wei)

5 (100)

faces

Icosahed  
ral:

20 (111)

faces

Cuboctah  
edral:

8 (111)

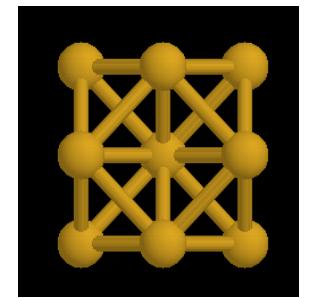
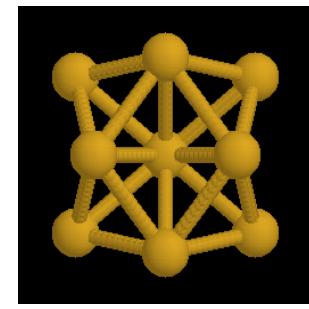
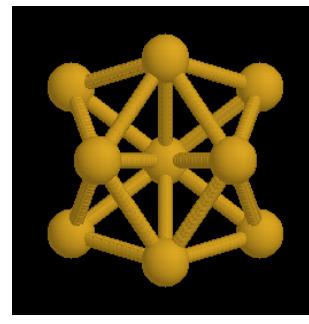
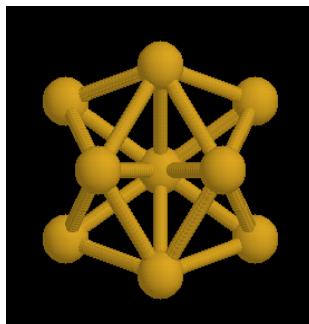
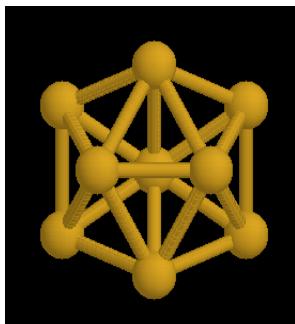
faces +

6 (100)

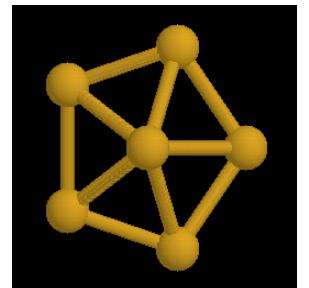
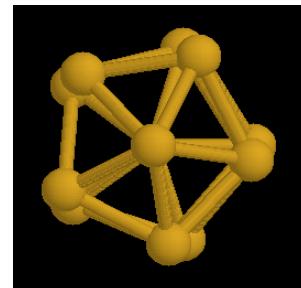
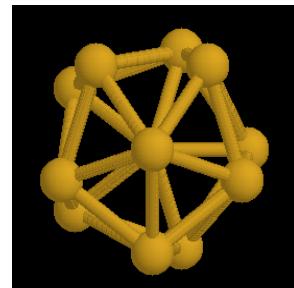
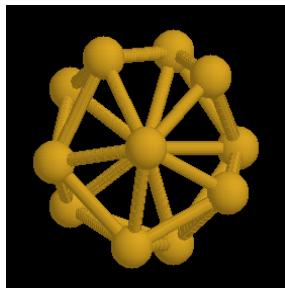
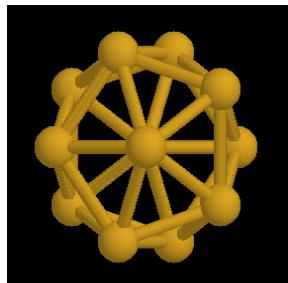
faces

## Structural phase transition

Icosahedral  $\leftrightarrow$  Cuboctahedral

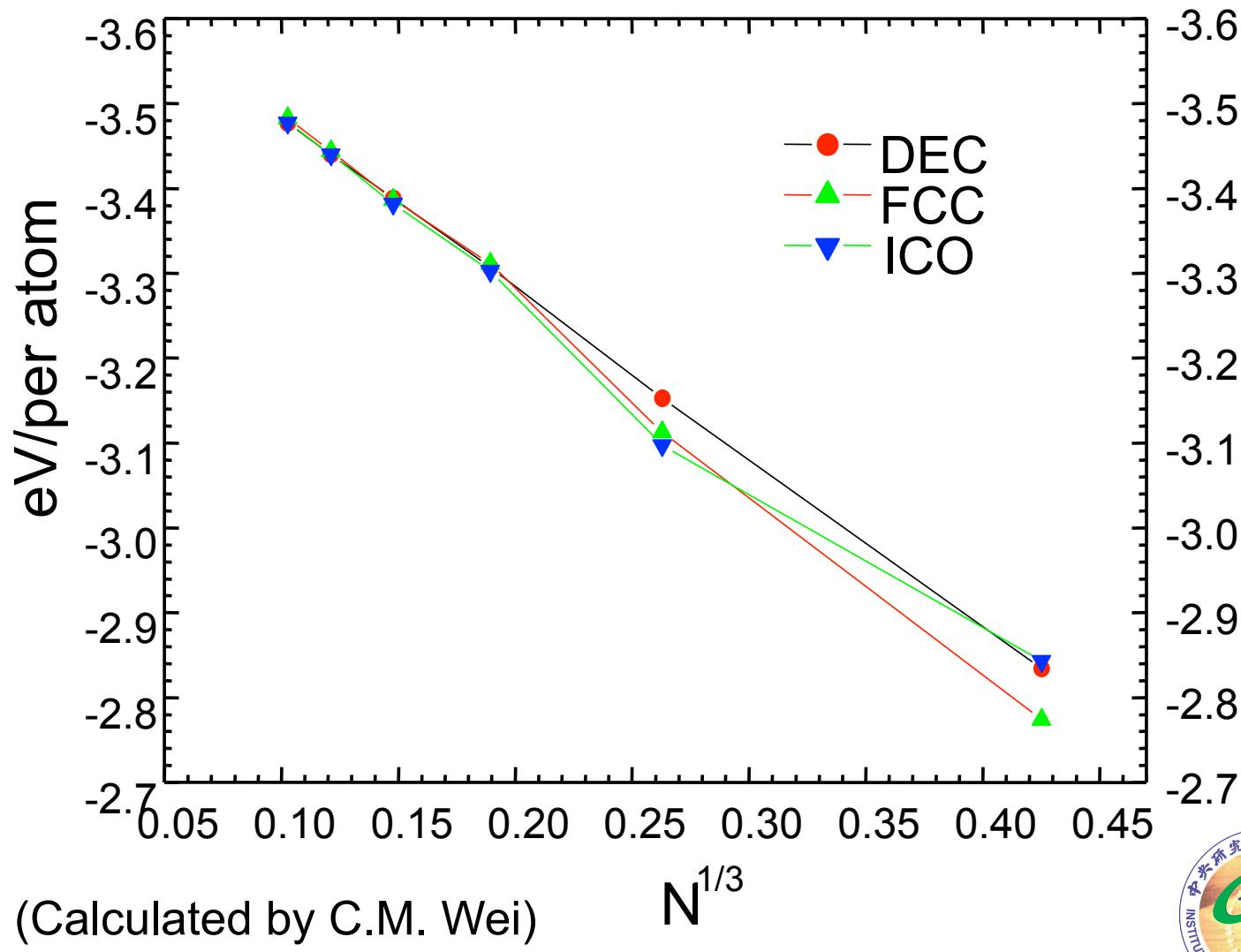


Icosahedral  $\leftrightarrow$  Decahedral



(Courtesy of C.M. Wei)

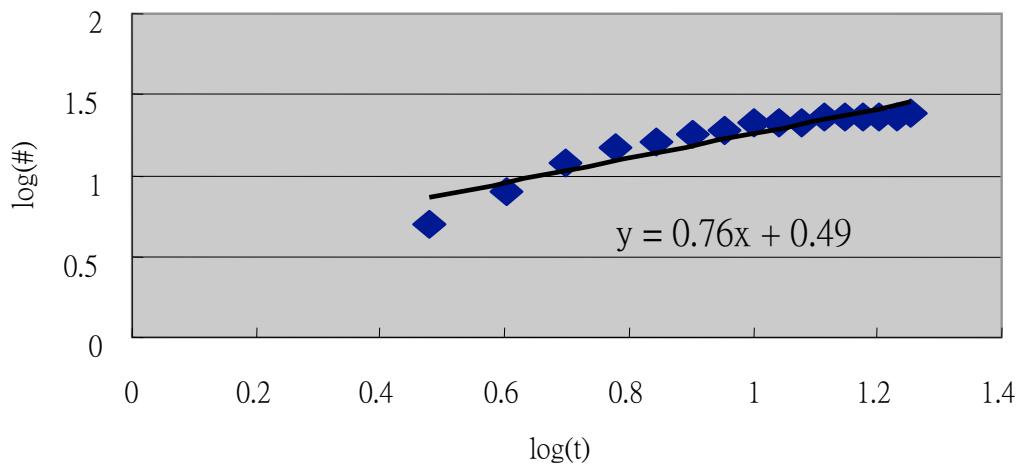
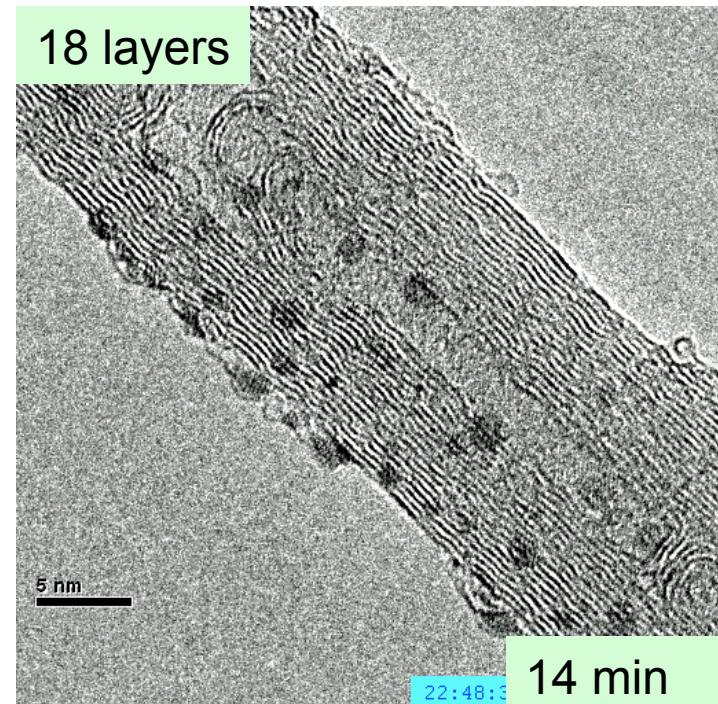
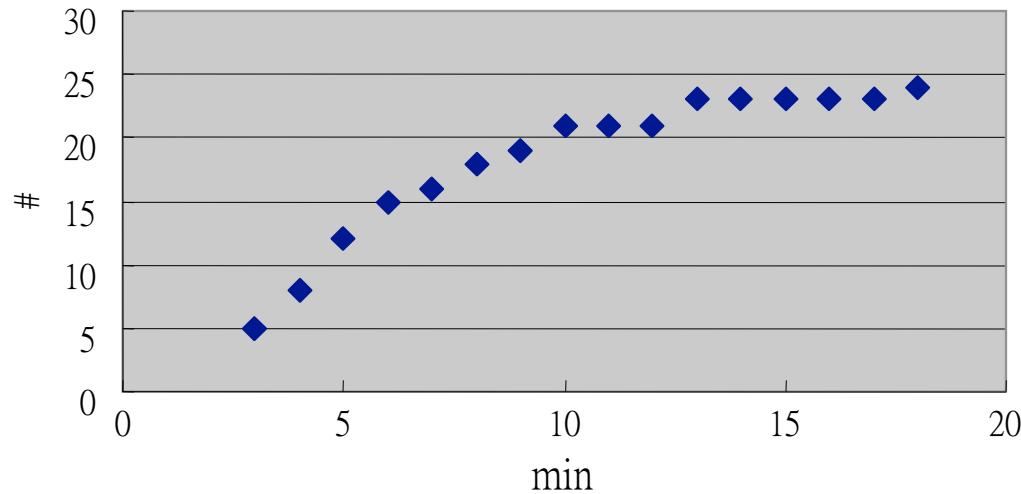
# Binding energy for Al nano particles



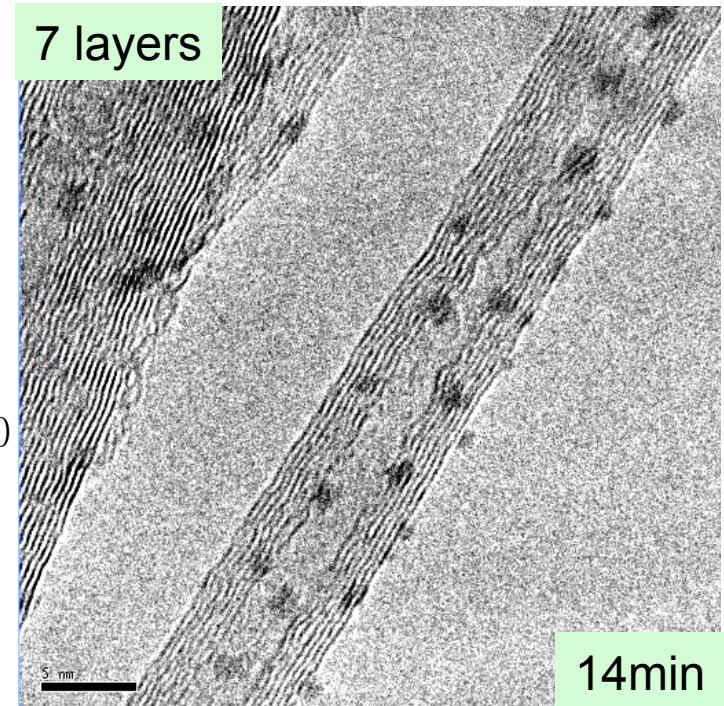
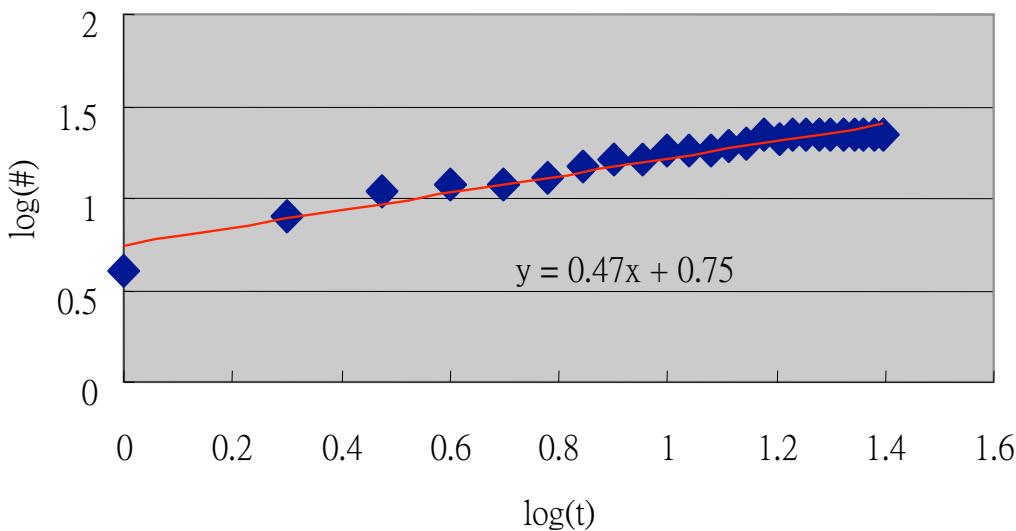
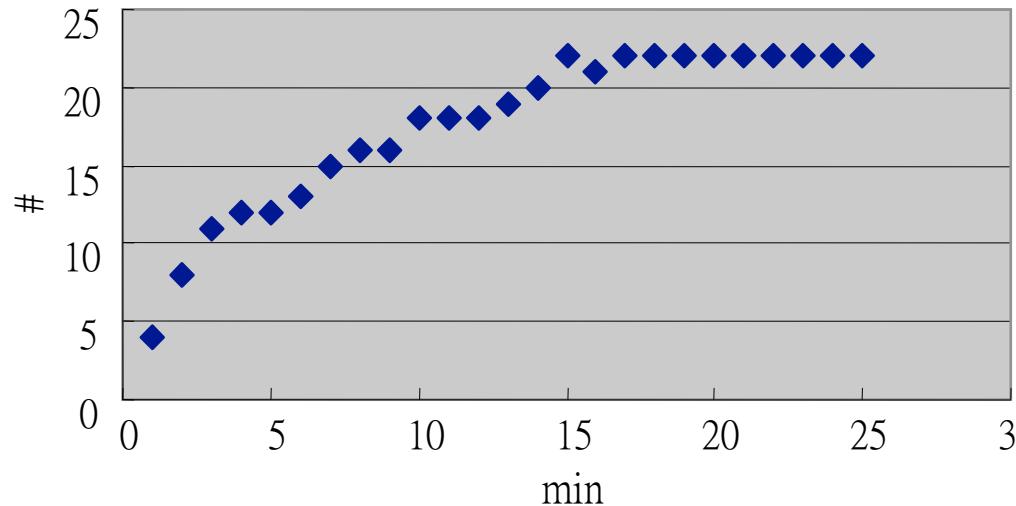
(Calculated by C.M. Wei)

$N^{1/3}$

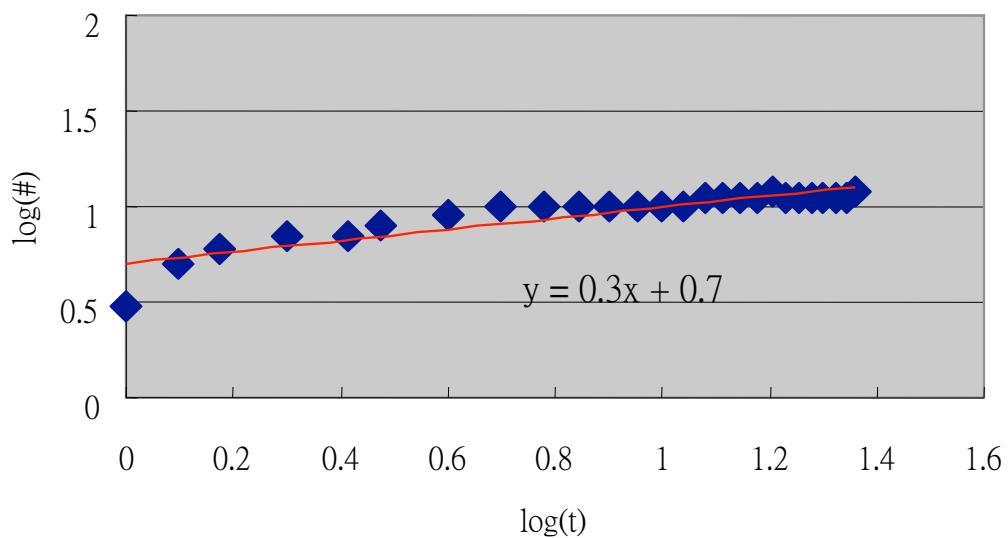
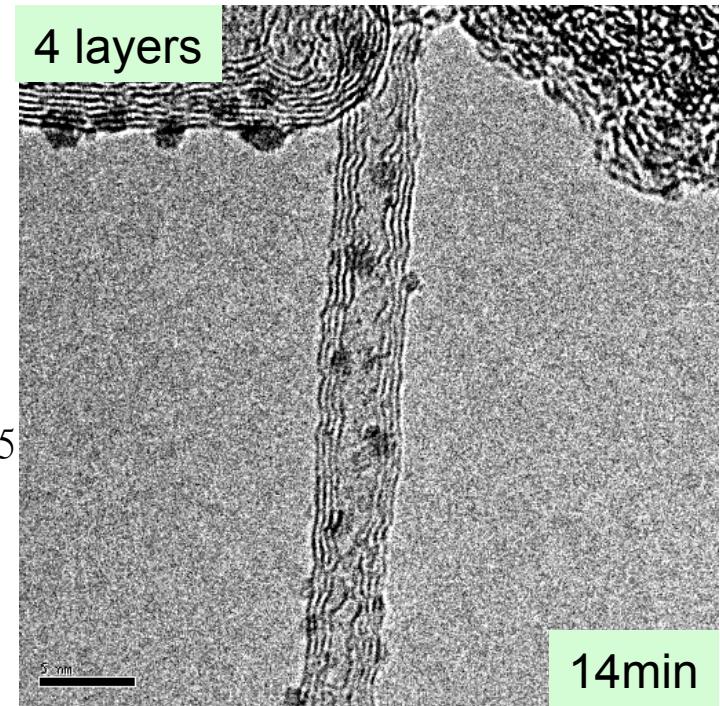
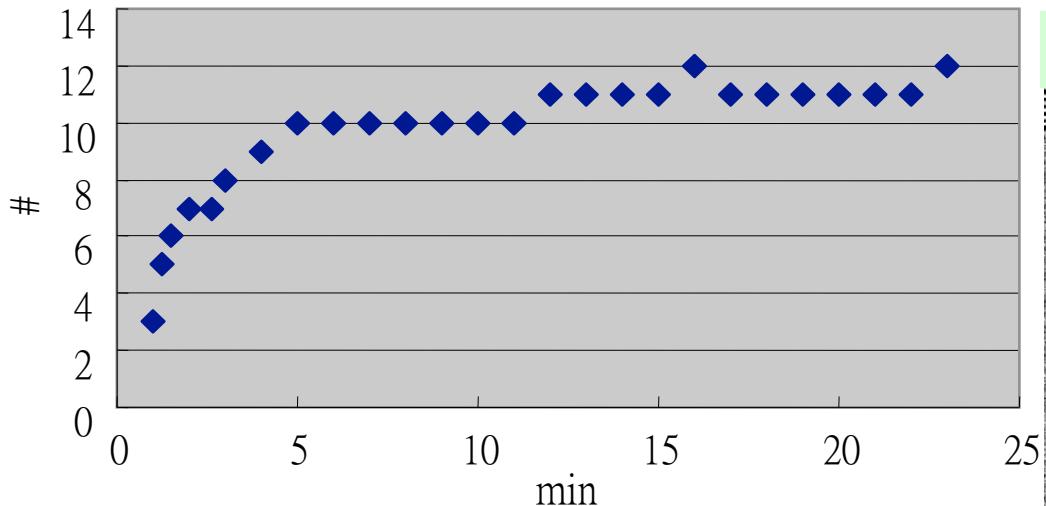
# **Growth of Ag clusters on 18-layer CNT**



# Growth of Ag clusters on 7-layer CNT



# ***Growth of Ag clusters on 4-layer CNT***



# How surface diffusion related to island density

In a 2D random walk, the diffusion coefficient is

$$D = \Gamma \cdot a^2$$

Where  $\Gamma$  is the number of jumps in unit time (second) and  $a$  is the jumping step size, i.e., lattice spacing.

The lifetime of an adatom is controlled by two collision rates,  $W_{AA}$  (adatom-adatom collision) and  $W_{AI}$  (adatom-island collision).

The “death rate” of adatom, i.e., # of adatoms die in unit time (sec) is

$$n/\tau_A = 2W_{AA} + W_{AI}$$

Where  $\tau_A$  is the lifetime, and  $n$  is the number density of adatoms --- # of adatoms per unit area.

Now, Let  $R$  be the deposition rate --- # of adatoms deposited on unit area in unit time, then

$$n = R\tau_A$$

The number of sites visited by an adatom during its lifetime is  $\Gamma\tau_A = D\tau_A/a^2$ . On average, # of sites occupied by one atom is  $1/na^2$  and # of sites occupied by an island is  $1/Na^2$ .

where  $N$  is the number density of islands --- # of islands per unit area.

Hence, the *probability* of an arriving adatom to collide with an existing atom is

$$(D\tau_A/a^2)/(1/na^2) = nD\tau_A$$

Similarly, the *probability* of an arriving adatom to collide with an existing island is

$$(D\tau_A/a^2)/(1/Na^2) = ND\tau_A$$

Multiplying the above two terms by  $R = n/\tau_A$  gives the collision rate, i.e., **# of collisions in unit time**:

$$W_{AA} = n^2D; \quad W_{AI} = nND$$

The nucleation rate, i.e., the rate of increase of the number density of islands, can be given as

$$dN/dt = W_{AA} = n^2D = R^2/(N^2D)$$

Substituting n with  $n = R/ND$ .

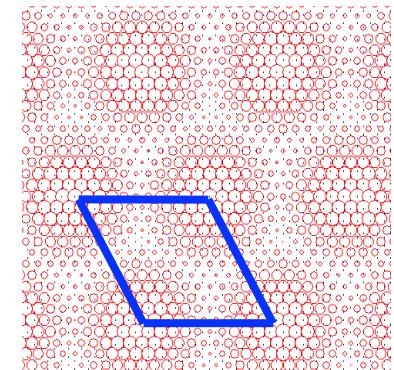
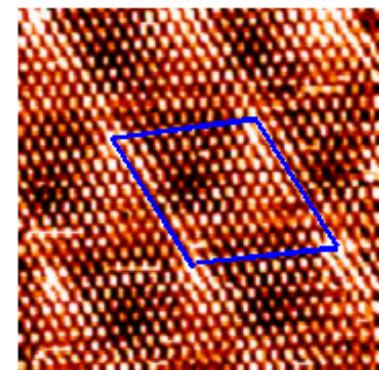
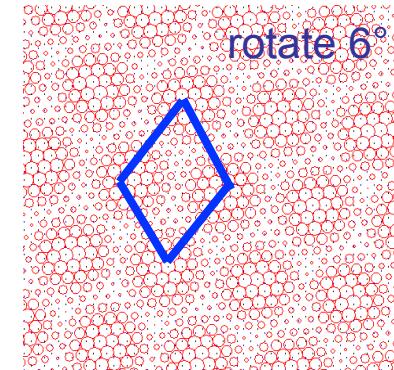
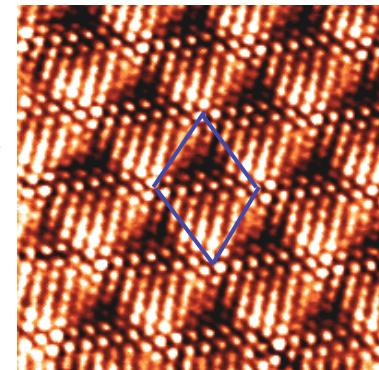
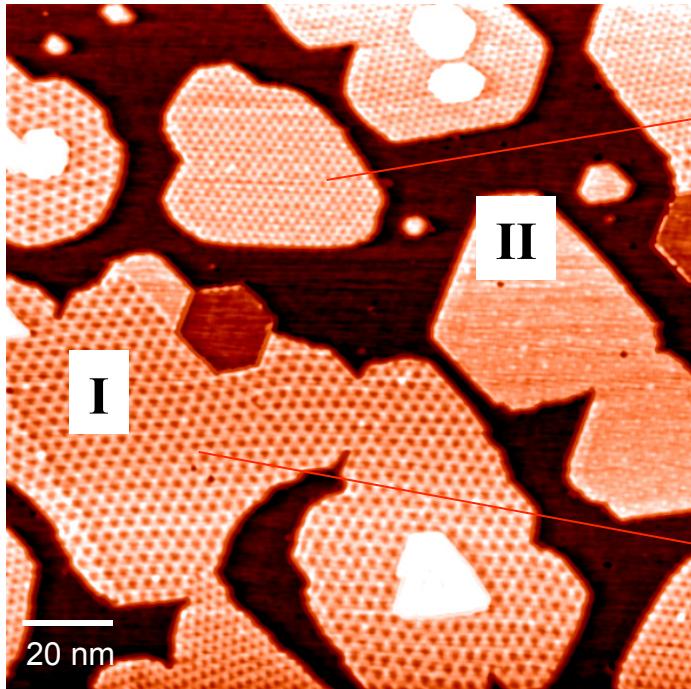
Then, integration leads to

$$N^3 = (3R^2/D)t = 3R\theta/D$$

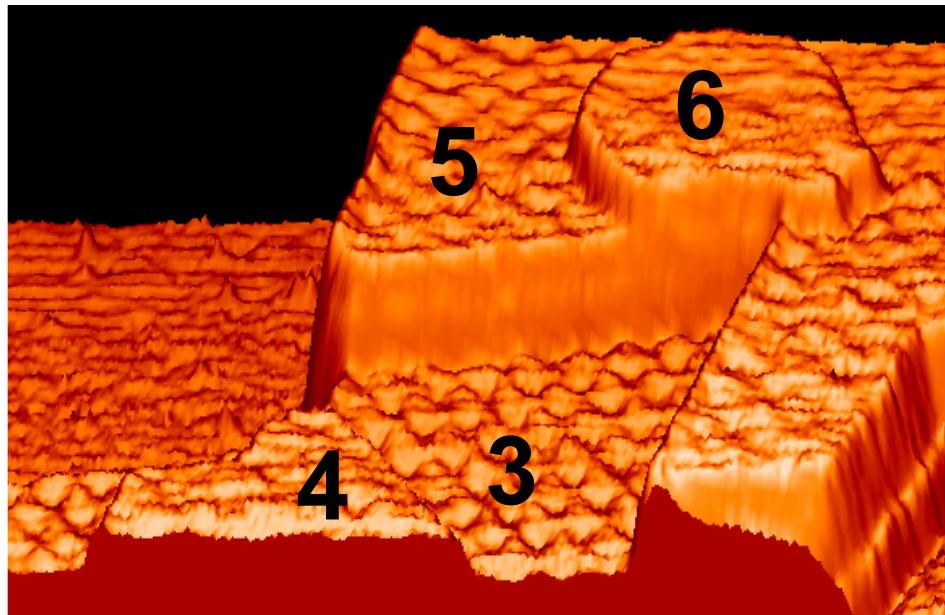
where,  $\theta = Rt$  is the total coverage up to time t.

Experimentally, we can measure N, and from there we can determine D.

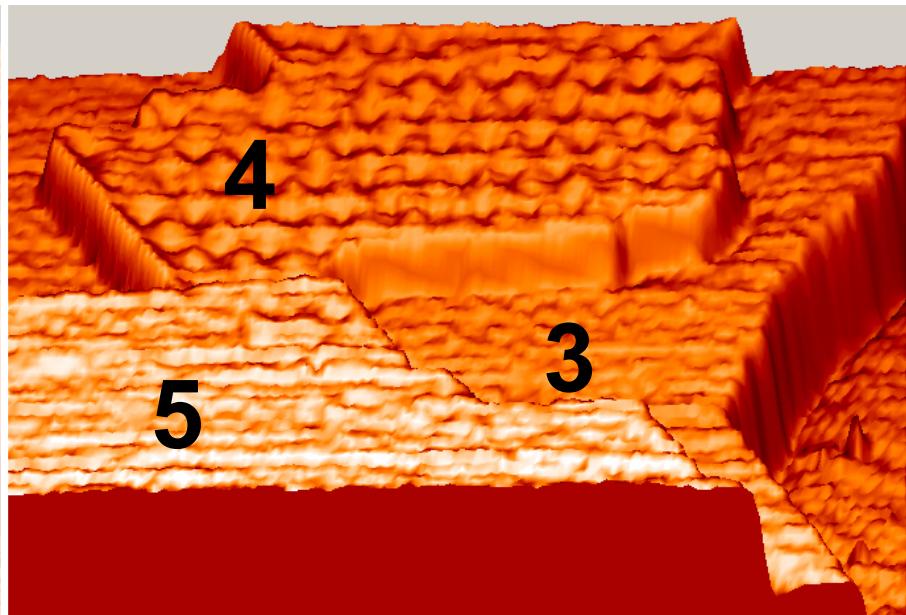
# Superstructures of 2D islands



# Characteristics of Pb island--- oscillatory and complementary contrast



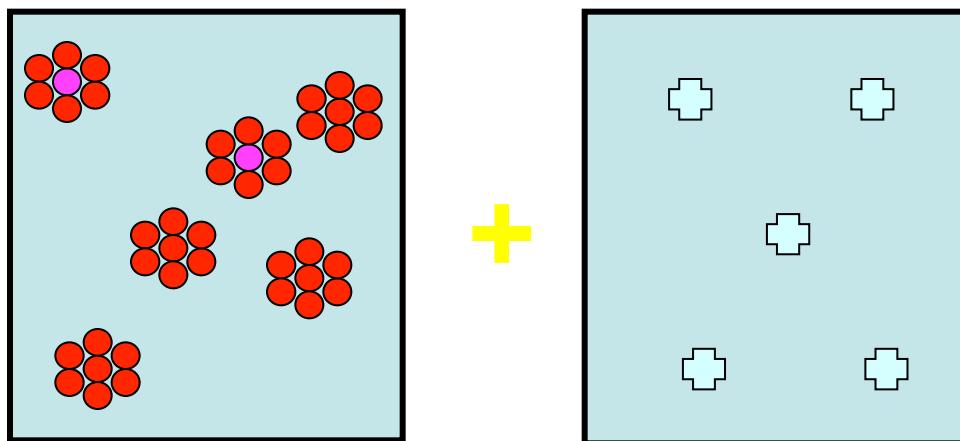
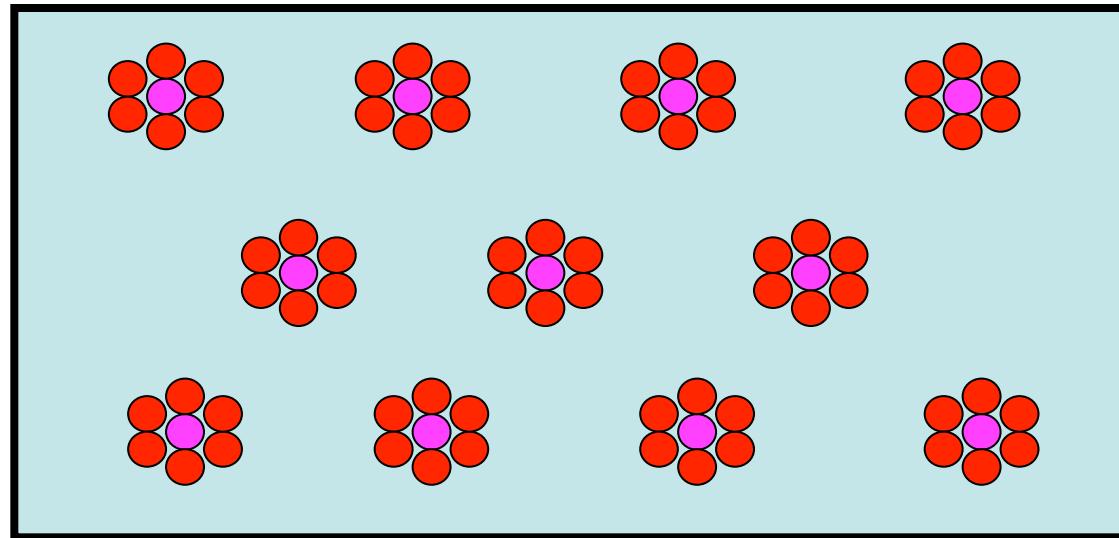
Type I



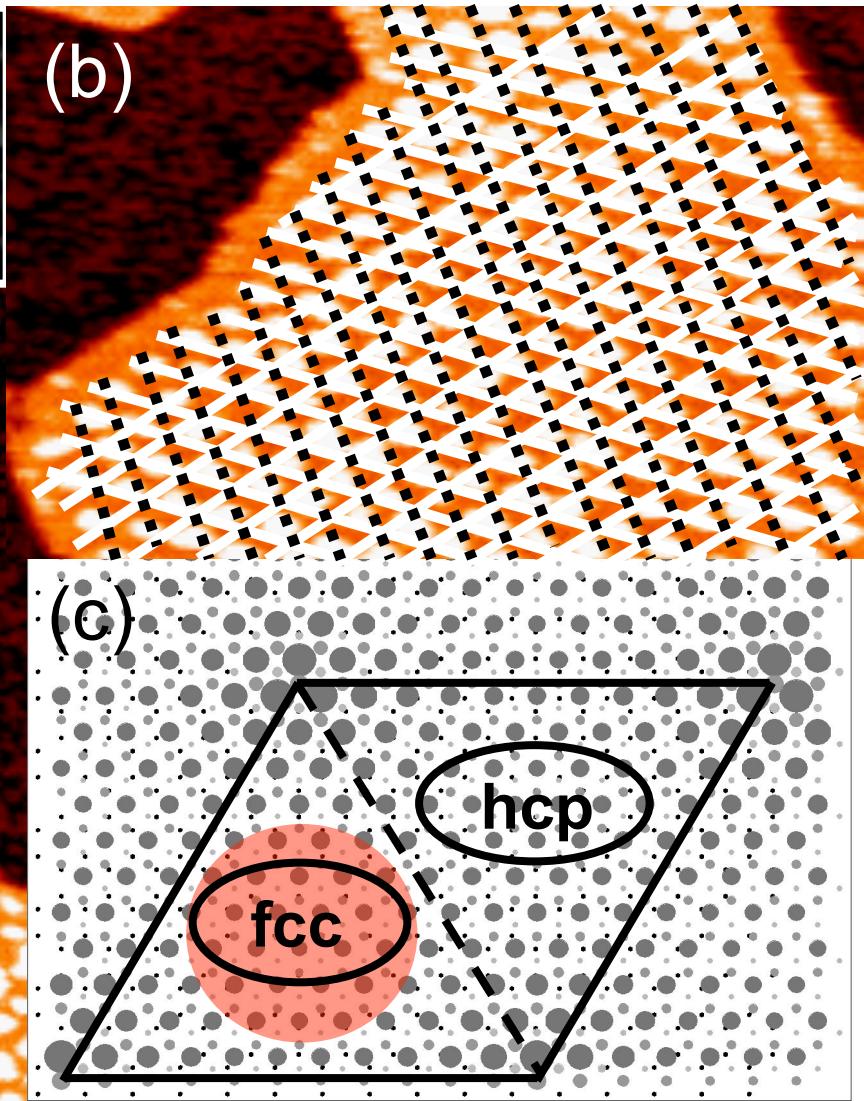
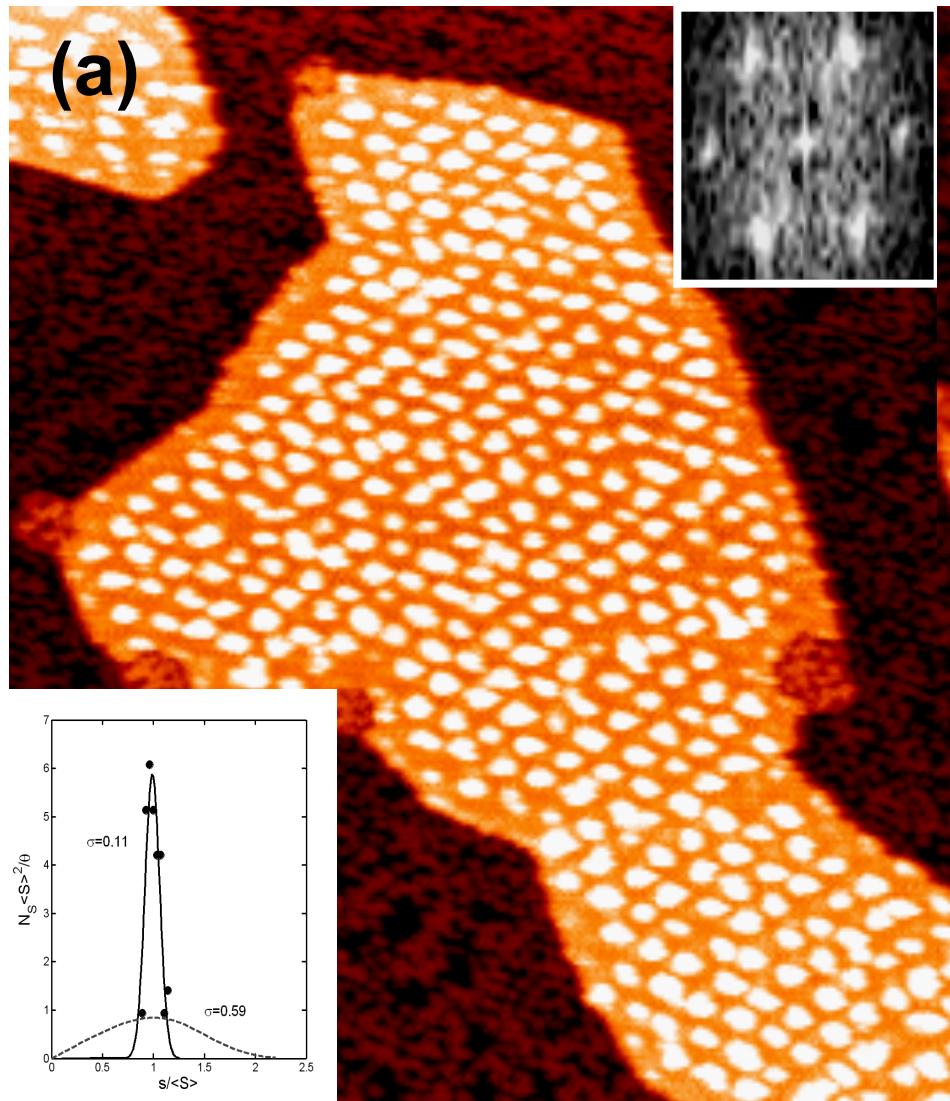
Type II

# Self-organized growth

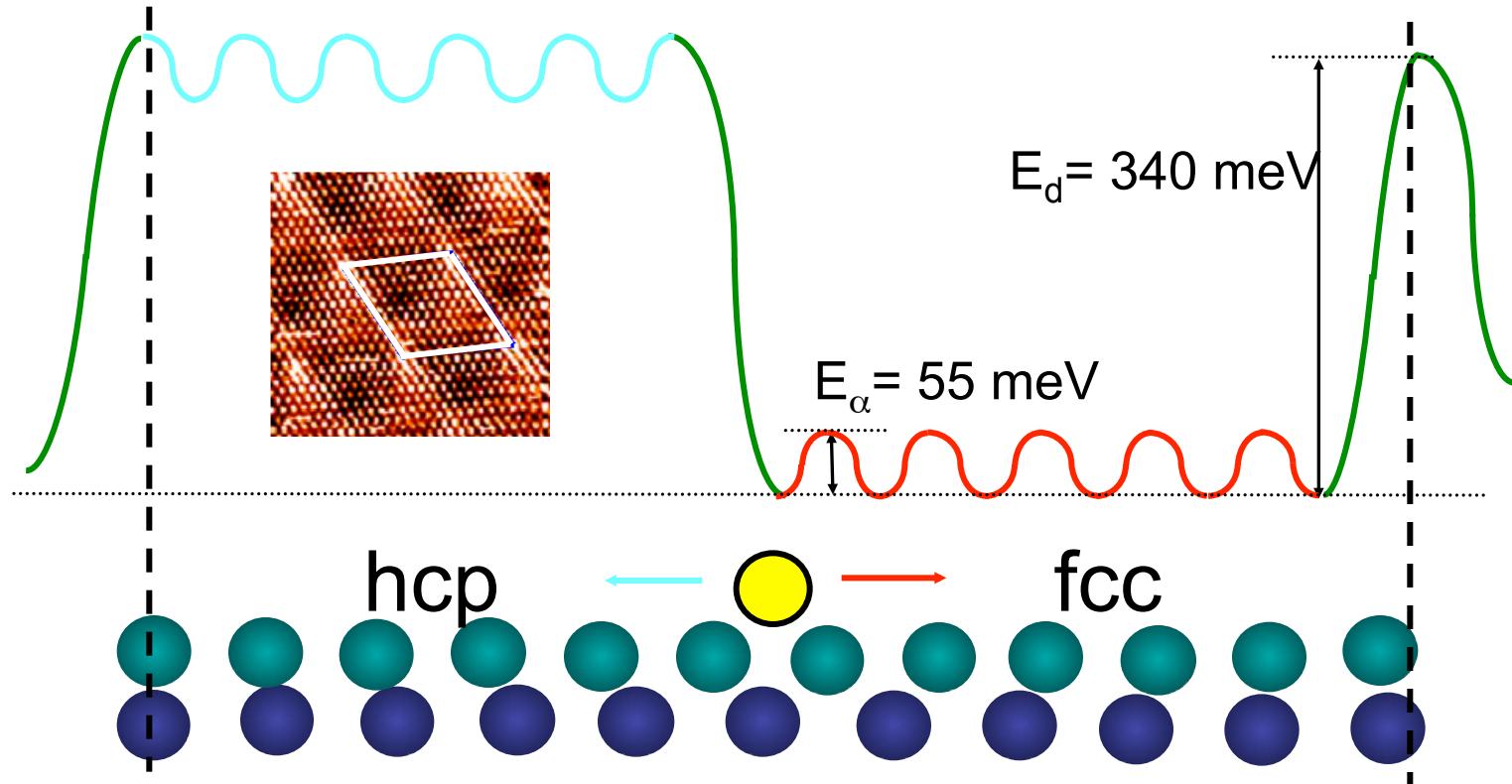
Size uniformity, Shape specification, Spatial orderliness and Functional homogeneity



# Properties of nanopucks on Pb islands

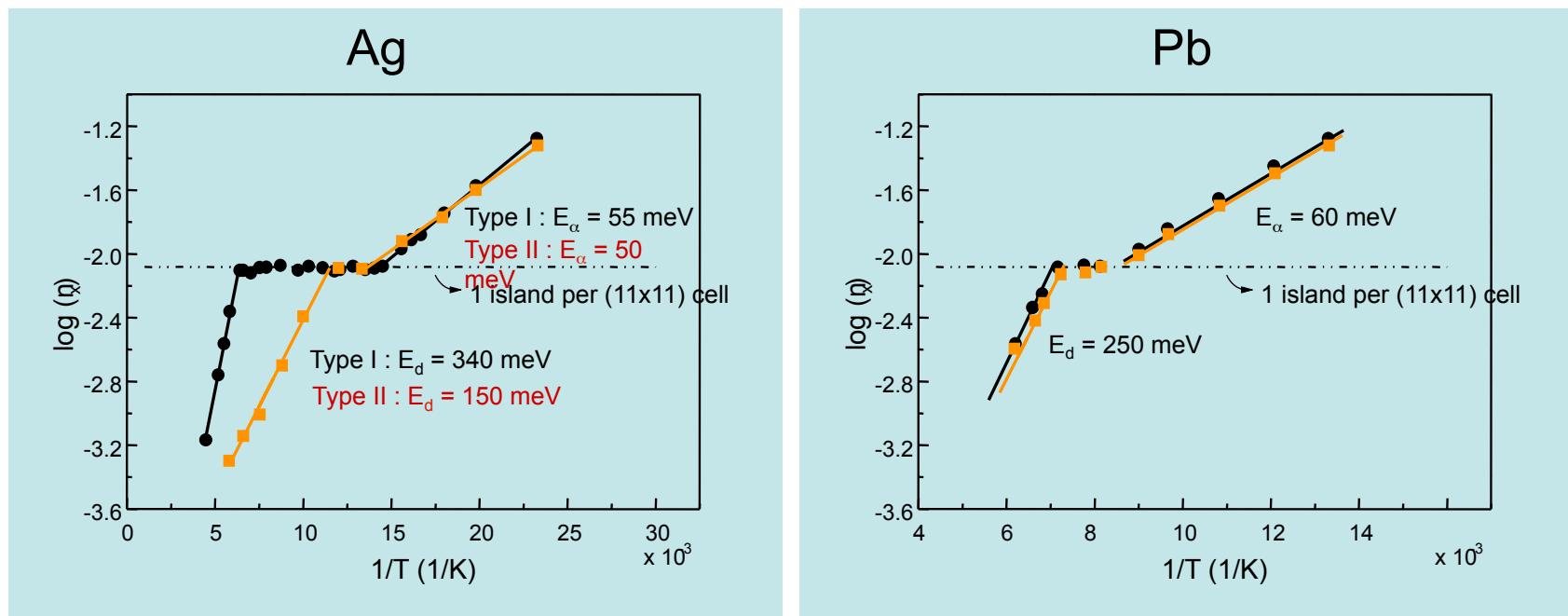
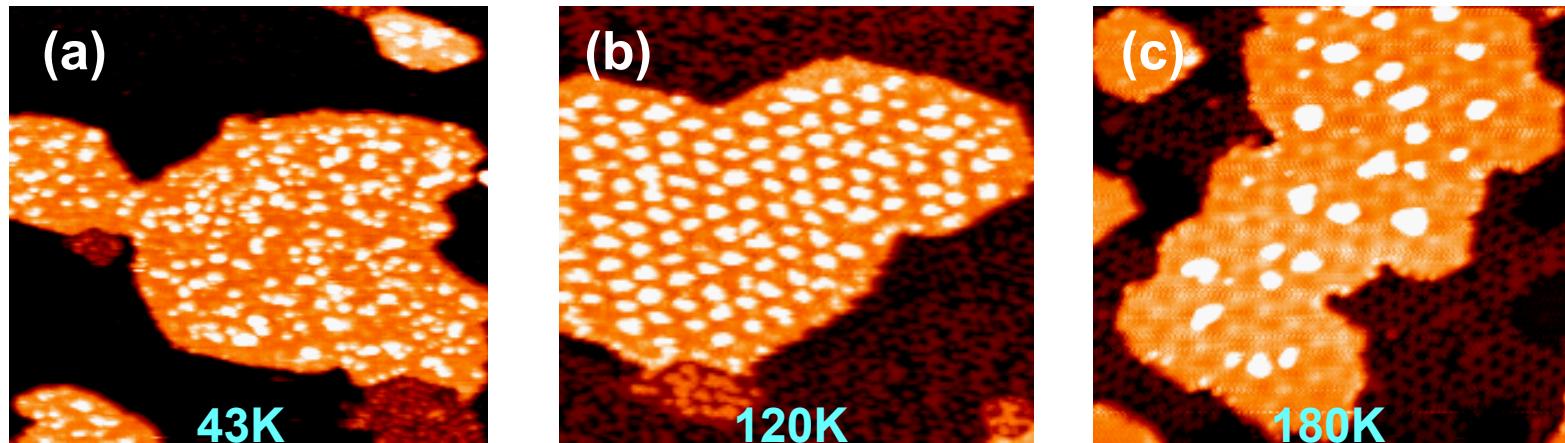


## Various diffusion barriers

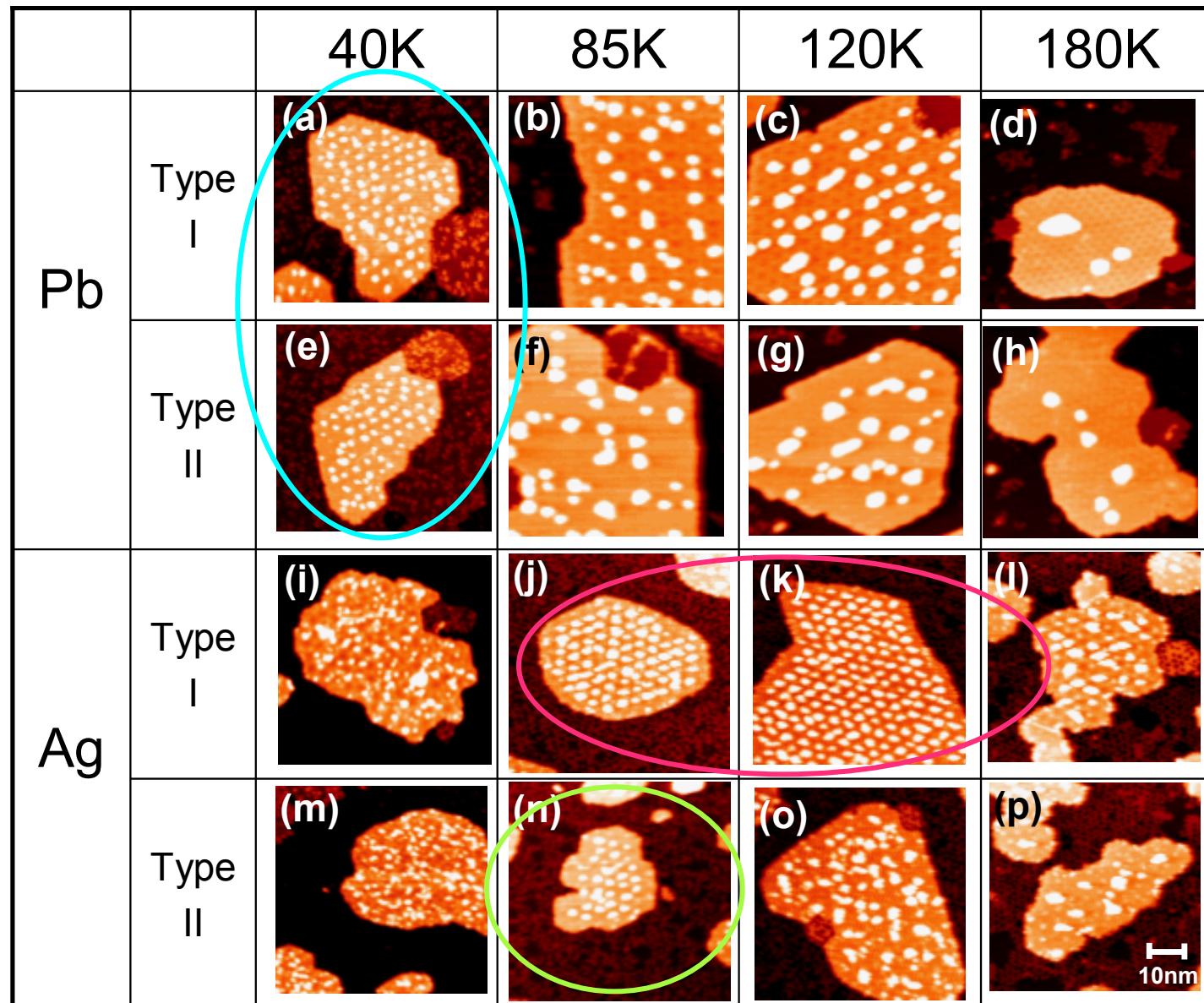


$$N \propto E_d / [(i+2)kT], \quad i : \text{number of atoms in critical nucleus}$$

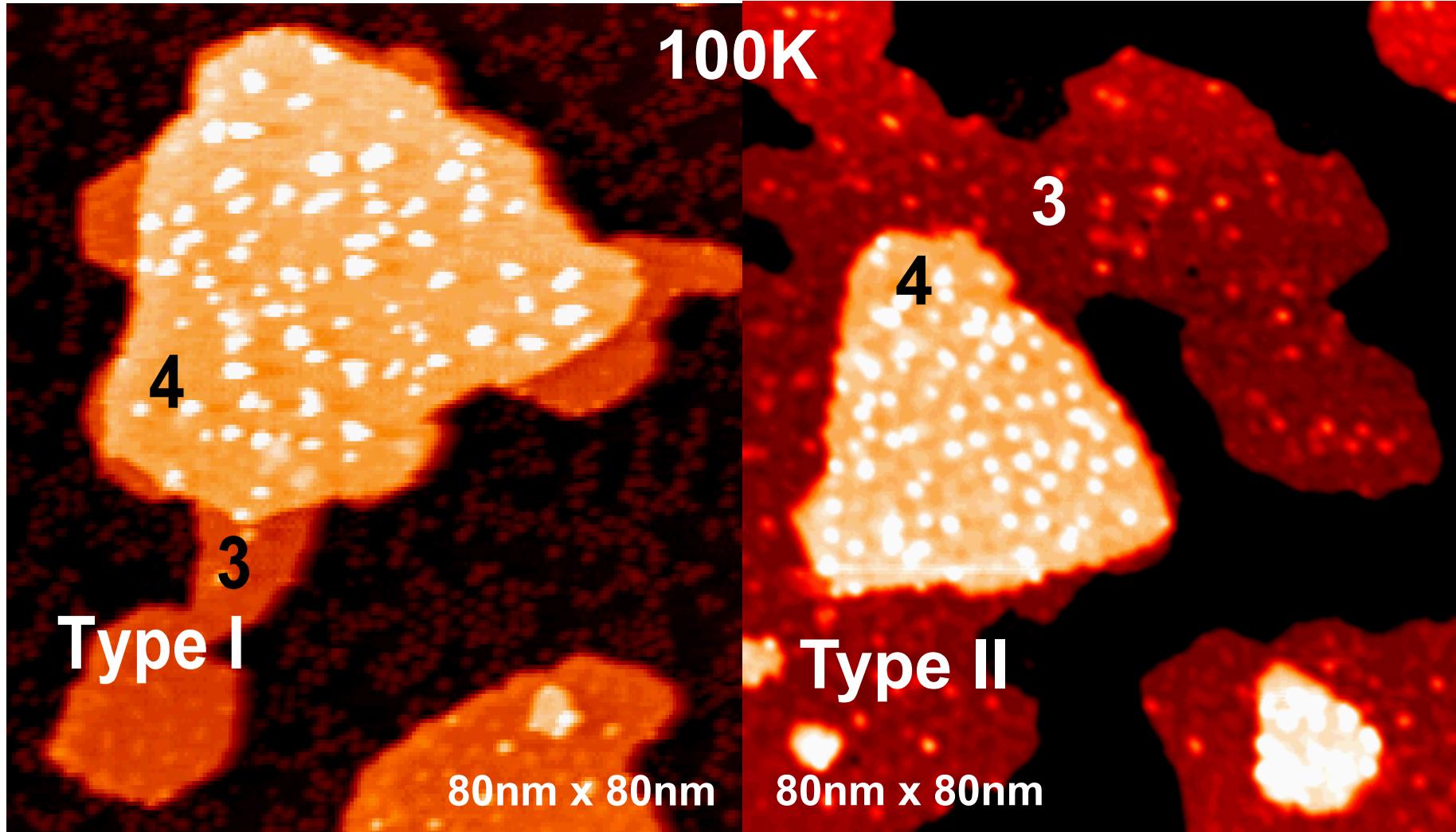
# Diffusion barriers for Ag and Pb nanopucks



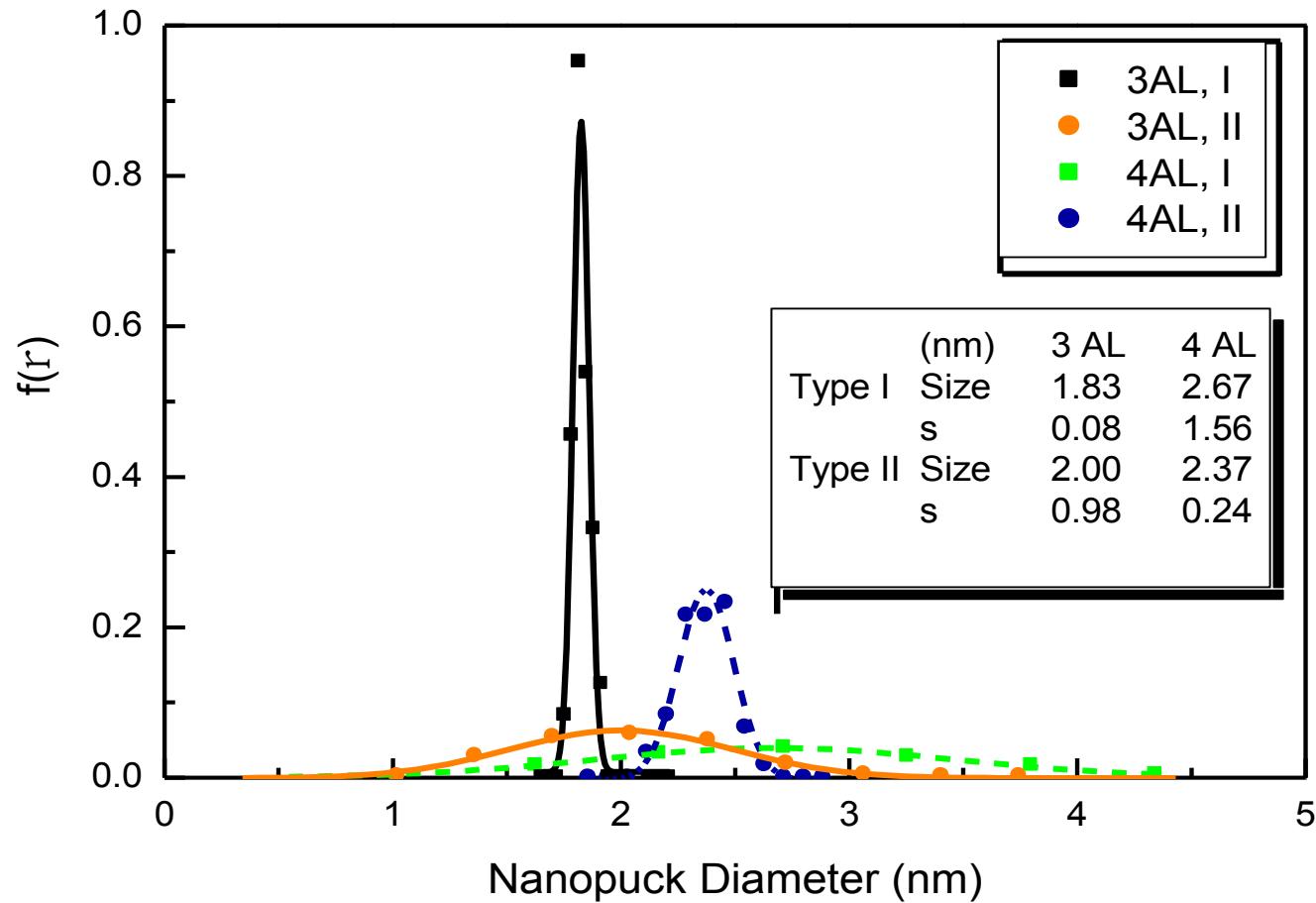
# Formation of Pb and Ag nanopucks



# Ag nanopucks on Pb islands of 4-layer thickness

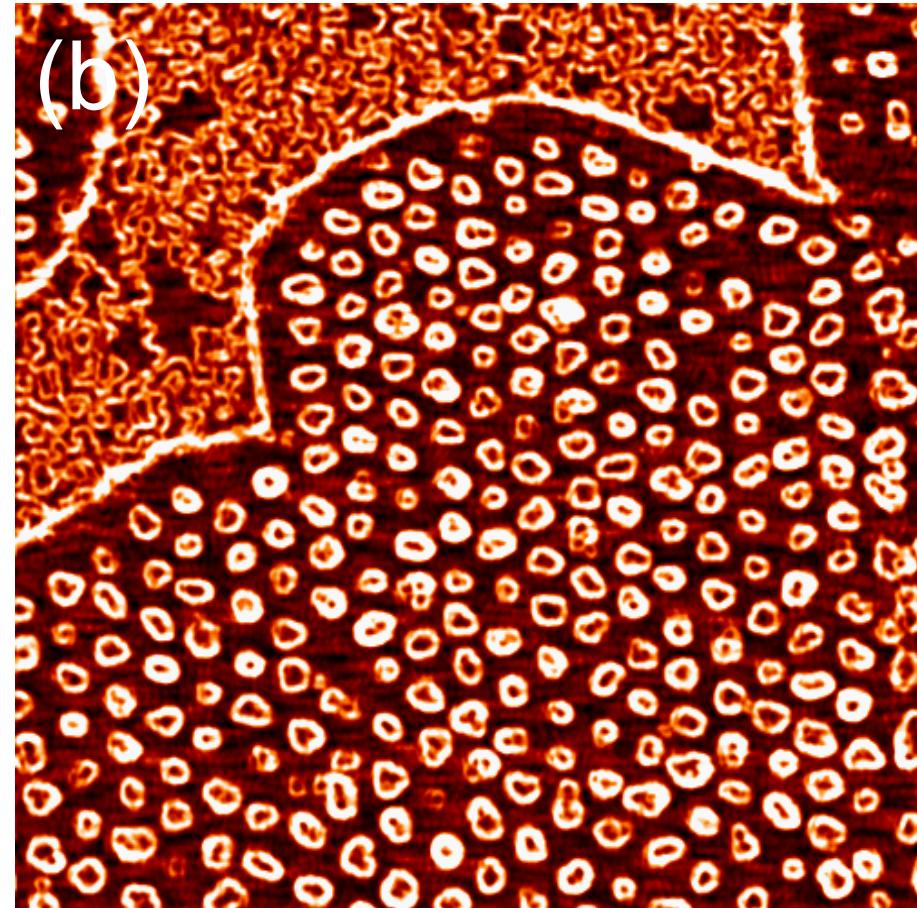
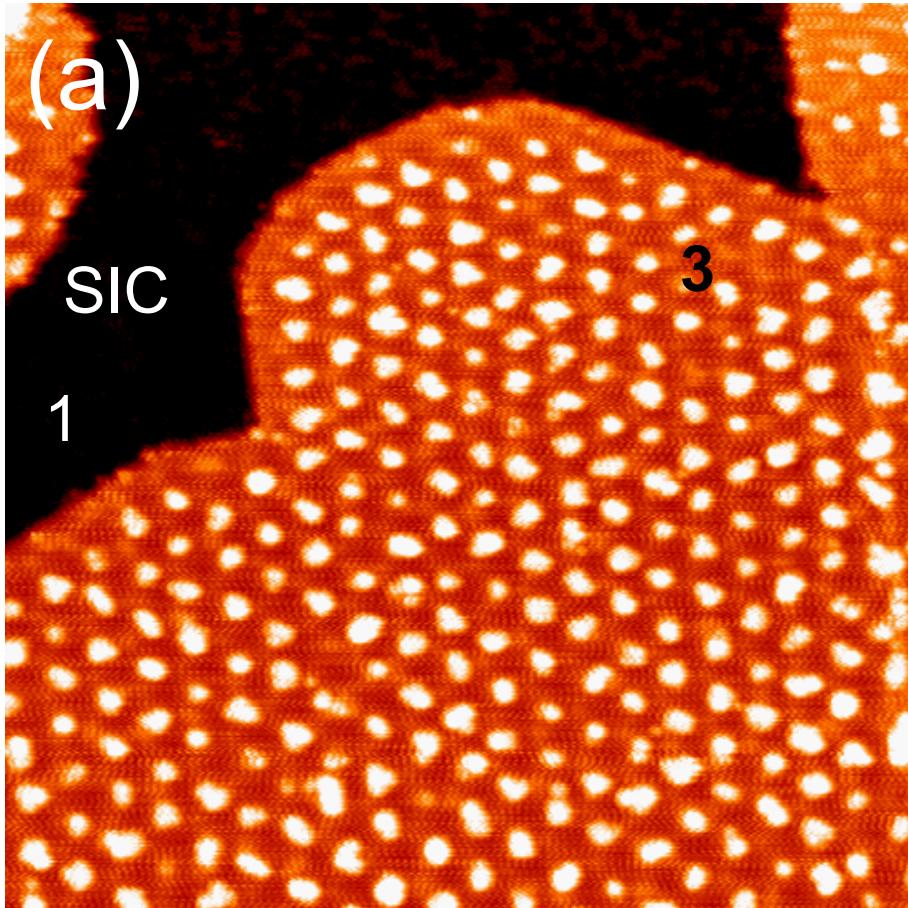


# Size distribution of nanopucks



Spatial orderliness : I (3AL) > II (4AL) > II (3AL) > I (4AL)

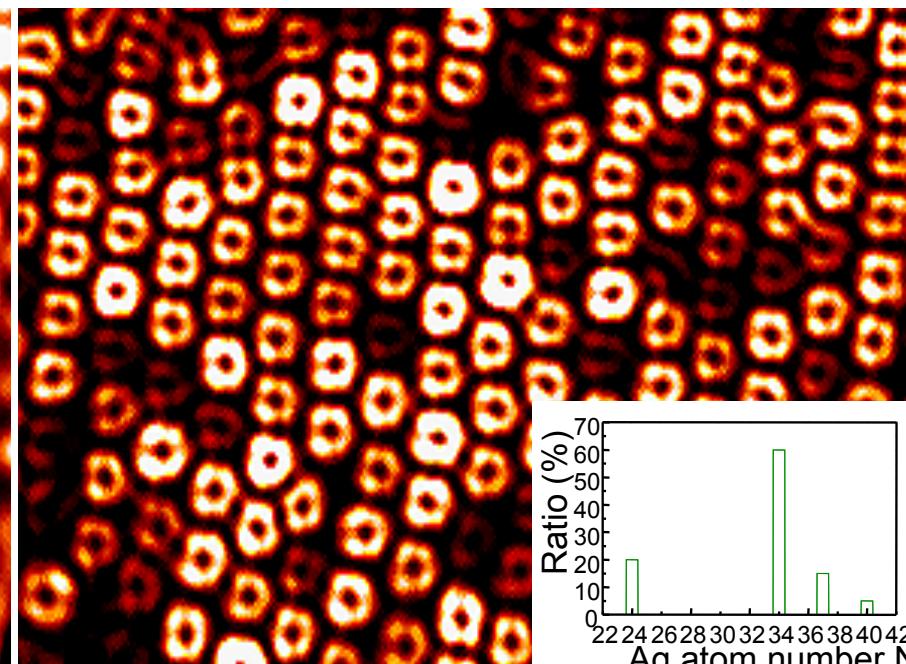
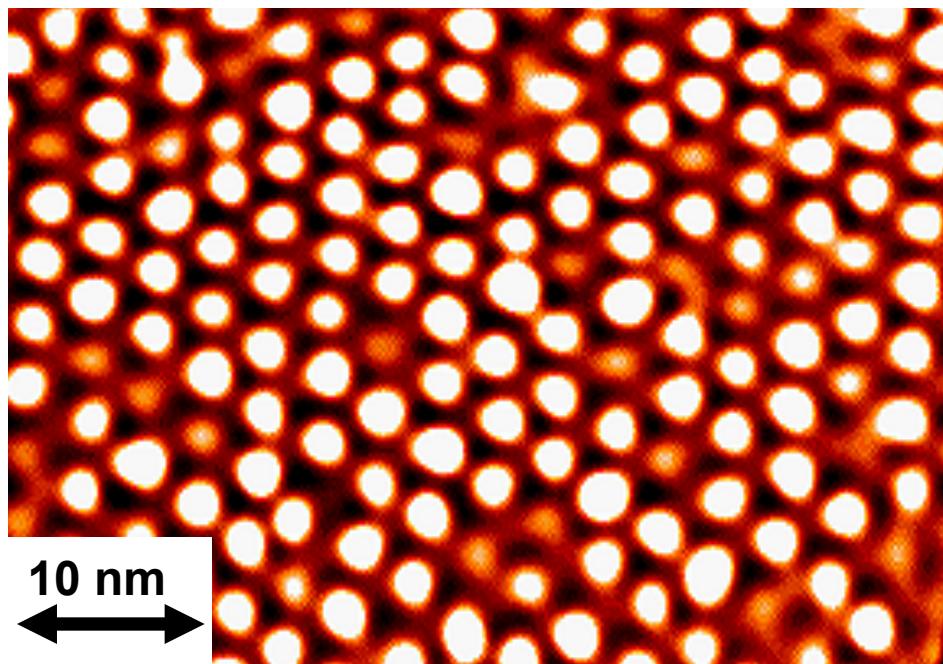
# Sizes and shapes of nanopucks



Ag 0.2 ML

$T = 120$  K

# Size-, site- & shape-controlled self-organized growth



# Summary

- *The quantitative derivations give the different binding energies of Ag adatoms on two triangular halves of a substrate unit cell.*
- *The difference in binding energy results in confined nucleation of Ag nanopucks at the fcc half cells exclusively and renders a site-specific arrangement.*
- *The order and size distribution of the nanopucks reveal a bi-layer oscillatory behavior, reflecting the electronic properties of the substrate.*